Overview of CNM LGAD results with B, Ga and C diffused Si-on-Si and epitaxial wafers

Lucía Castillo García on behalf of IFAE pixel group and CNM - 9th September 2021

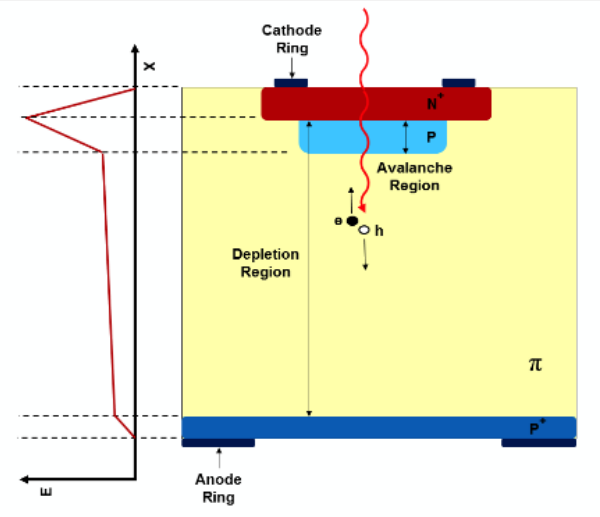
WORKSHOP ON PICO-SECOND TIMING DETECTORS FOR PHYSICS

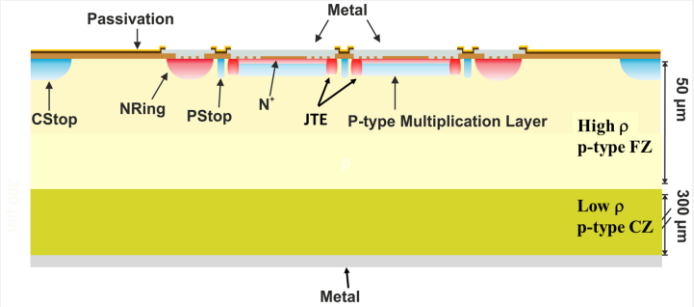
Outline

- Motivation
- Radiation damage
- CNM LGAD technologies (Si-on-Si and low resistivity epitaxial wafers)
- LGAD performance
  - Electrical characterization (IV/CV)
  - Auto-triggering measurements → define operating voltages
  - Beta source measurements for single pad sensor
    - Collected charge
    - Time resolution
  - Transient Current Technique (TCT) measurements
    - Inter-pad (IP) gap on 2×2 LGAD arrays
    - Gain on single pad sensors
- Summary and outlook

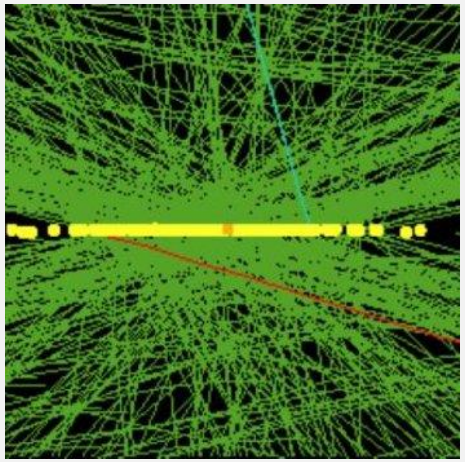
Motivation

- **L**ow **G**ain **A**valanche **D**iode (LGADs) sensors
  - Originally developed by CNM to explore the possible improvement towards radiation hardness (through charge multiplication)
  - Later proposed for timing applications
    - Achieving a time resolution of about 30 ps before irradiation
- Interest to study LGADs and their performance at **high fluences beyond 10^{15} n_{eq}/cm^2**
  - Performance remains challenging due to degradation of the gain layer
  - Investigate new doping materials (B, Ga), substrates and new geometries
  - Deliver thin sensors providing good time resolution, fine segmentation, radiation hardness
- ATLAS and CMS experiments have chosen the LGAD technology for the **H**igh **G**ranularity **T**iming **D**etector (HGTD) and for the **E**nd-Cap **T**iming **L**ayer (ETL)
  - ATLAS : 4 fC at 2.5×10^{15} n_{eq}/cm^2 at (max) 600 V, 50 ps time resolution (talk)
  - CMS : 10 fC at 1.5×10^{15} n_{eq}/cm^2 at (max) 600 V, 50 ps time resolution (talk)





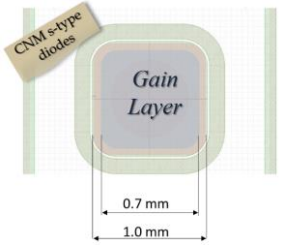
Radiation damage



- Silicon pixel detectors are especially important for the precise determination of tracks and vertices, enabling the selection of interesting events through the identification of b-jets (b-tagging)
- Particle accelerators are improved to further probe the energy frontier delivering higher energies and **increasing the number of collisions per unit time**
- At High Luminosity LHC (HL-LHC):
  - The number of collisions per bunch crossing will be increased
  - The instantaneous luminosity will be approximately a factor of ~5 higher than the LHC nominal values
  - Several LHC experiment sub-systems will require an upgrade in order to **cope with the high rate, hit occupancy and radiation environment**
- Two main types of radiation damage:
  - **Bulk damage** due to Non Ionizing Energy Loss (NIEL)
    - Effective doping concentration, acceptor removal, leakage current, trapping
  - **Surface damage** due to Ionizing Energy Loss (IEL)
    - Accumulation of positive charge
- **New solutions have to be found** for the silicon sensors and the associated front-end electronics

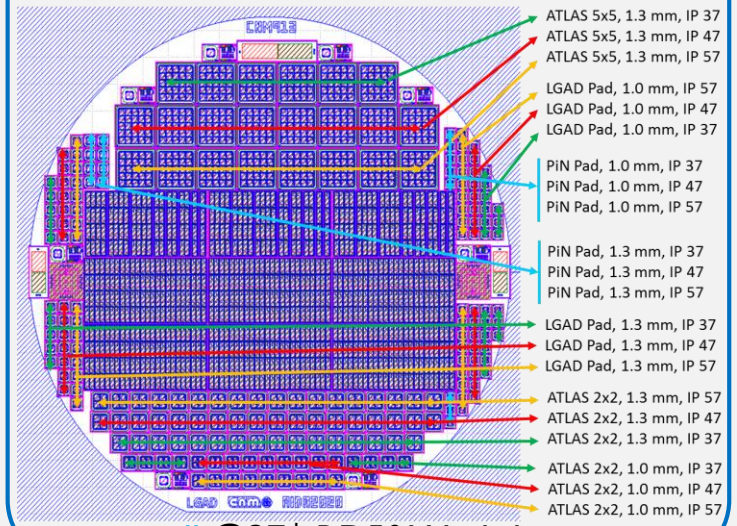
CNM LGAD technologies

- **CNM Run 10478 B, B+C, 10924 Ga (2017-2018)**
  - 50 µm active thickness
  - 4" Si-on-Si wafers
  - W4 B: $V_{gl}{\sim}38V, V_{fd}{\sim}42V, V_{bd}{\sim}130V$
  - W5 B+C: $V_{gl}{\sim}38V, V_{fd}{\sim}42V,$ $V_{bd}{\sim}110-140V$
  - W6 Ga: $V_{gl}{\sim}32-64V, V_{fd}{\sim}40-80V, V_{bd}{\sim}140V$
  - Expected gain higher than 20
  - B dose: 1.5×10^{13} at/cm^2
  - Ga dose: 6×10^{13} at/cm^2



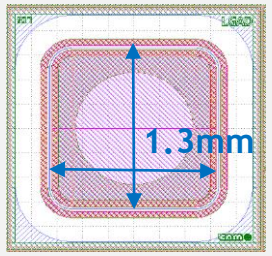
talk@30th and talk@32nd RD50 Workshop

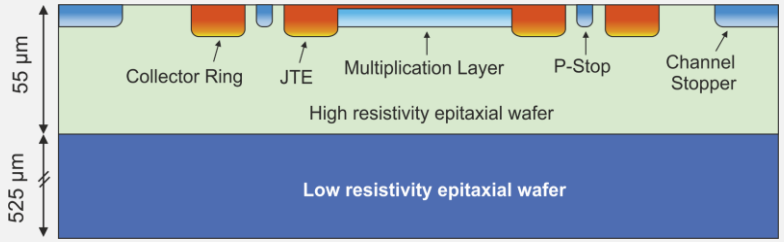
- **CNM Run 12916 AIDA2020**
  - 50 µm active thickness
  - Si-on-Si wafers
  - $V_{gl}{\sim}38V, V_{fd}{\sim}42V, V_{bd}{\sim}85V$ at room temperature
  - B dose: 1.8×10^{13} at/cm^2



talk@37th RD50 Workshop

- **CNM Run 13002 EPI (2021)**
  - 6" epitaxial wafers
  - 55/525 µm
  - Substrate resistivity = 0.001-1 Ωcm
  - Epi-layer resistivity ~ 200 Ωcm
  - $V_{gl}{\sim}30V, V_{fd}{\sim}35V, V_{bd}{\sim}400V$ at room temperature
  - B dose: 2×10^{13} at/cm^2

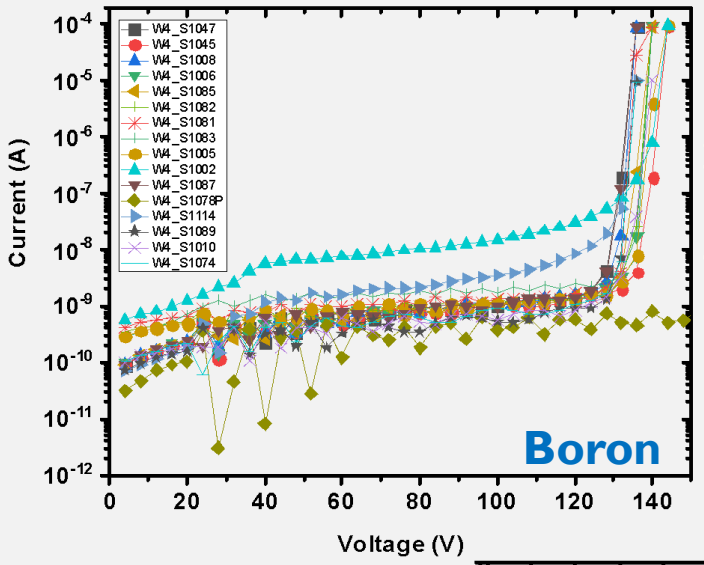


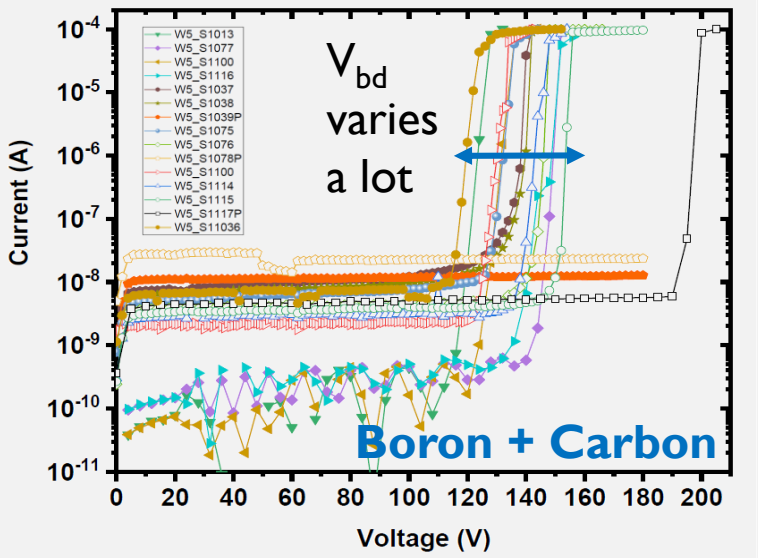


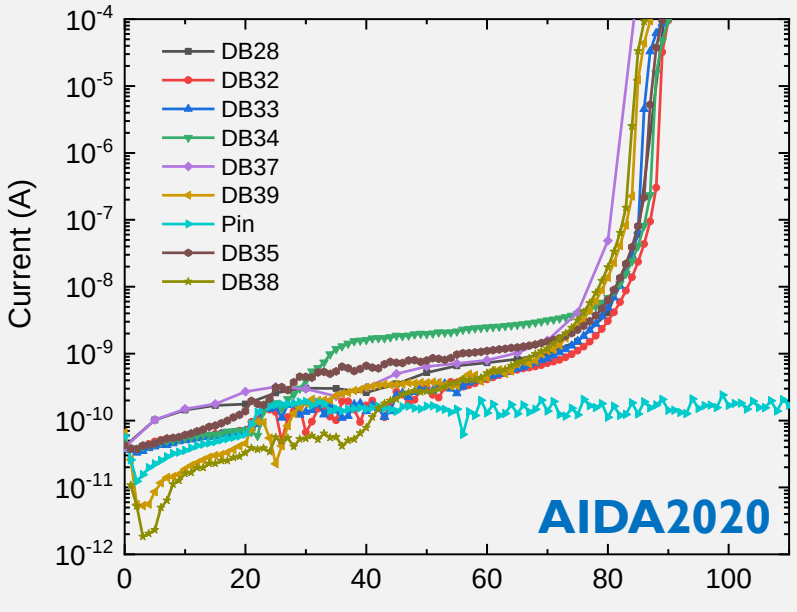
talk@RD50 Workshop

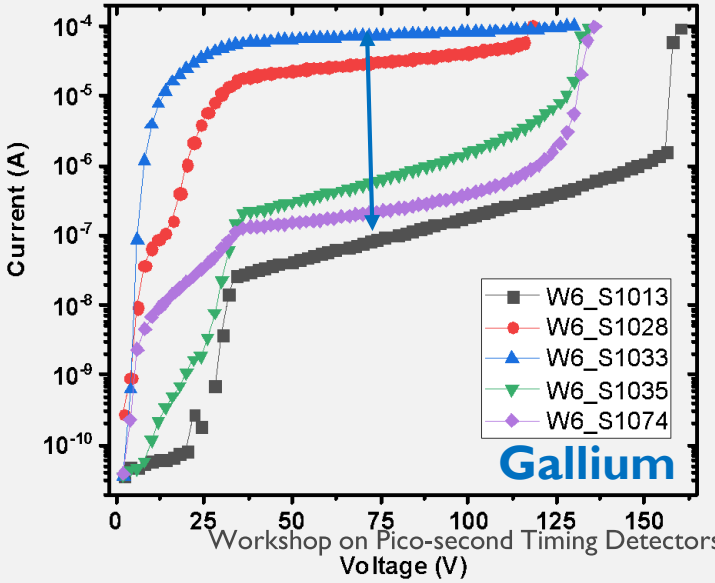
Electrical characterization (I-V room temperature)

Unirradiated devices

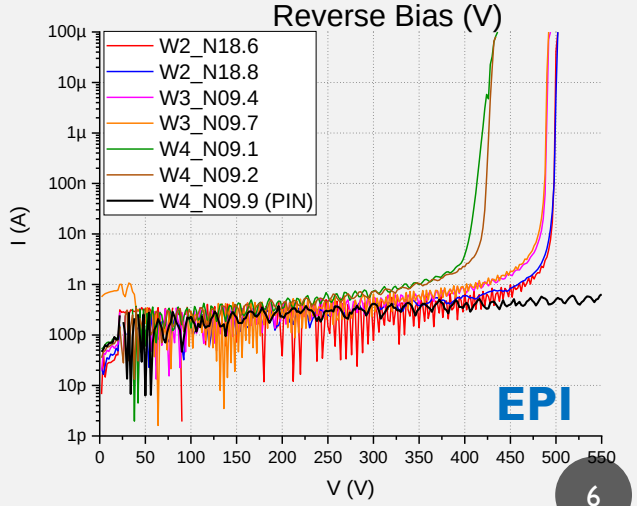






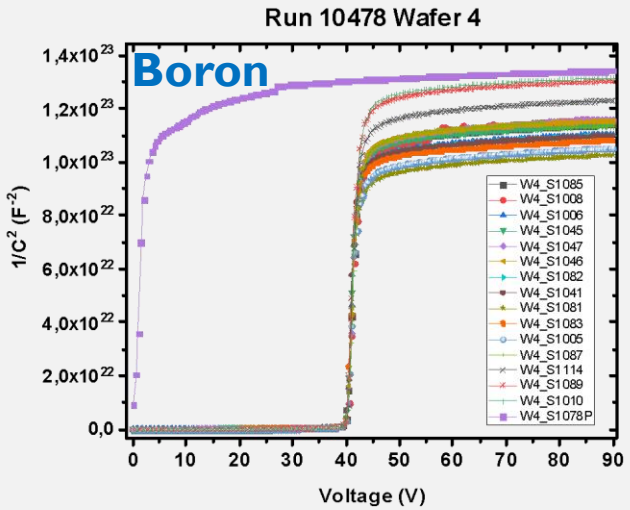


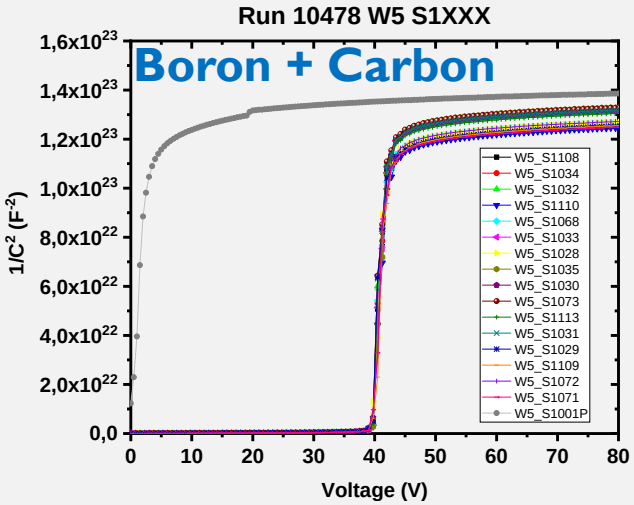
High current due to multiplication

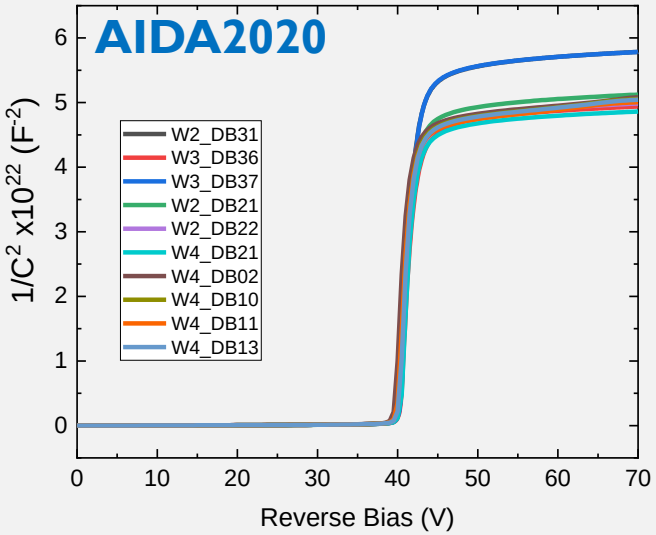


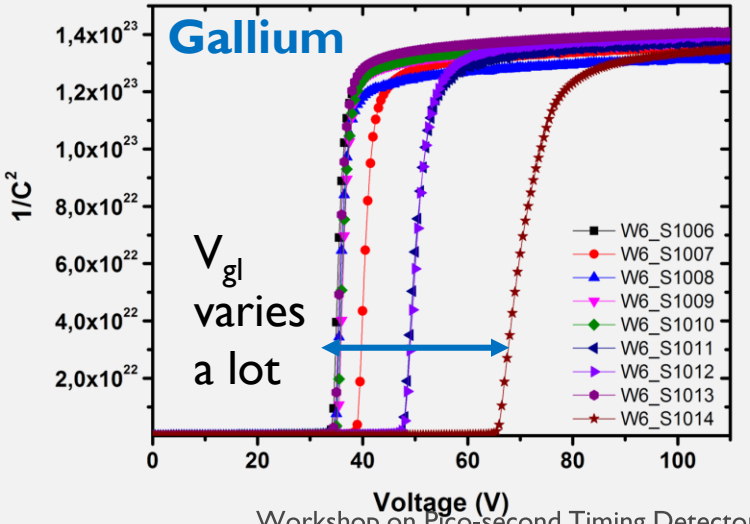
Electrical characterization (C-V room temperature)

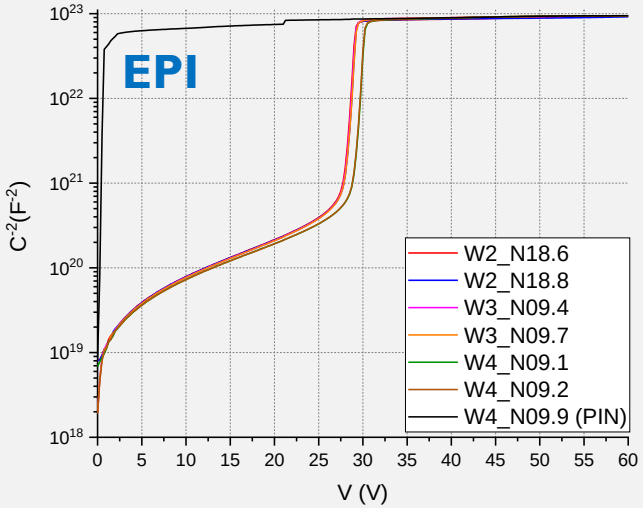
Unirradiated devices







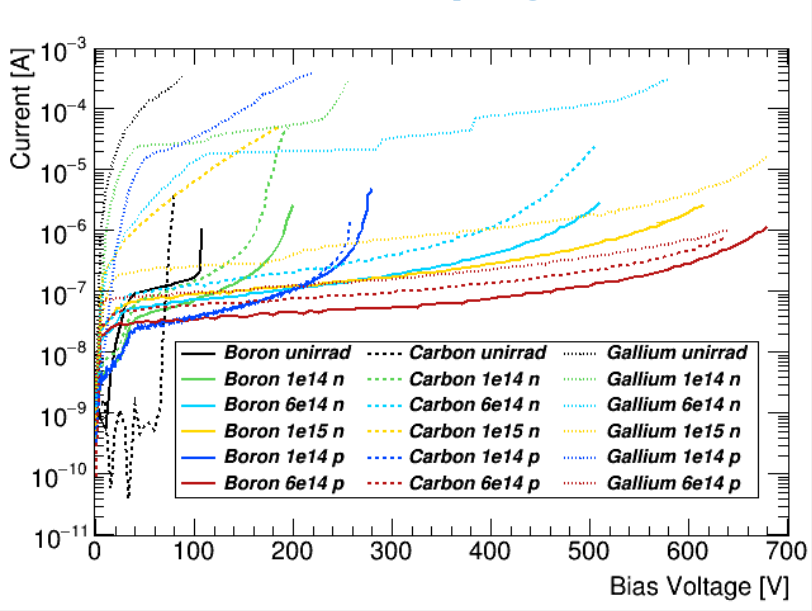




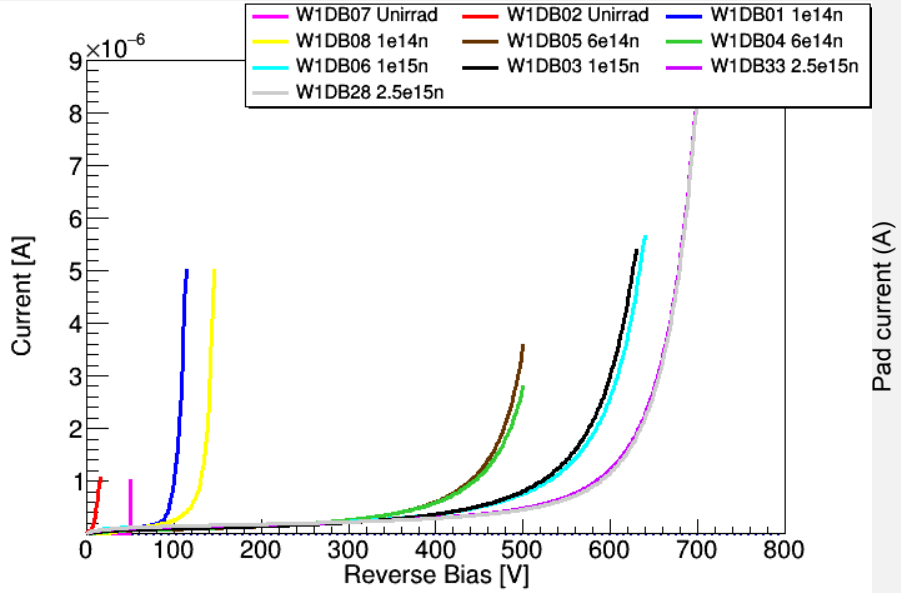
Electrical characterization (I-V -30 °C)

Irradiated devices

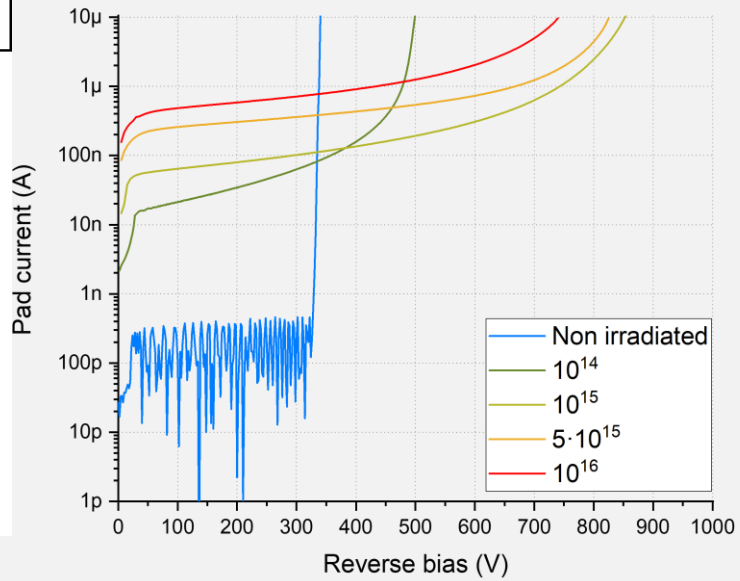
B, B+C and Ga doping $T = -30°C$



AIDA2020 $T = -30°C$



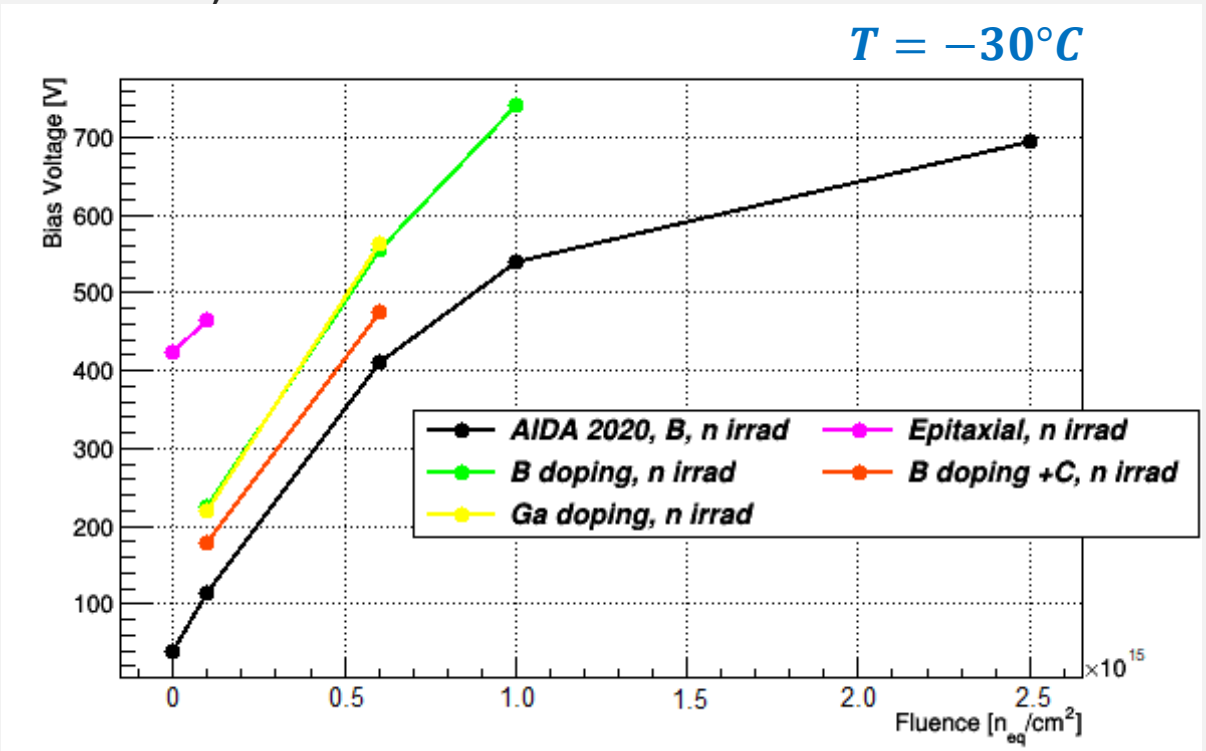
EPI $T = -20°C$



- Ga high current from multiplication
  - Sensor close to breakdown after depletion
- Early breakdown due to higher dose of wafer implant wrt old B run
- Breakdown is happening at higher voltages

Operational voltage

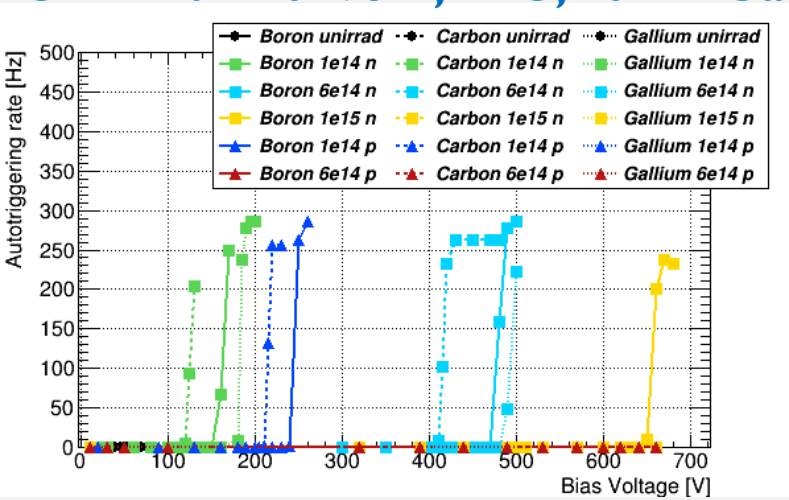
- The limitation on operating voltages is given by auto-triggering studies
- LGADs at high bias voltages present self pulses (w/o external source)
- We need to make sure that a coincidence event from both tested sensors is a real one, not a fake → need to ensure sensor is not auto-triggering
- Auto-triggering events have waveforms that are identical to real events
- Estimate the frequency of these events
- Trigger on different threshold values for different bias voltages (here only showing 10 mV~5σ_{noise})
- Maximum voltage with an acceptable auto-triggering rate of 1 kHz
- Subsequent measurements are taken up to bias voltage without auto-triggering



Auto-triggering studies

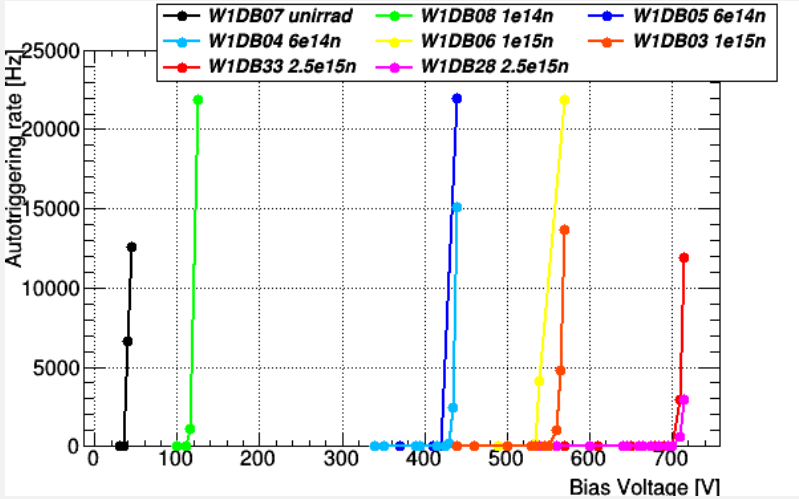
$T = -30°C$

CNM Run 10478 B, B+C, 10924 Ga



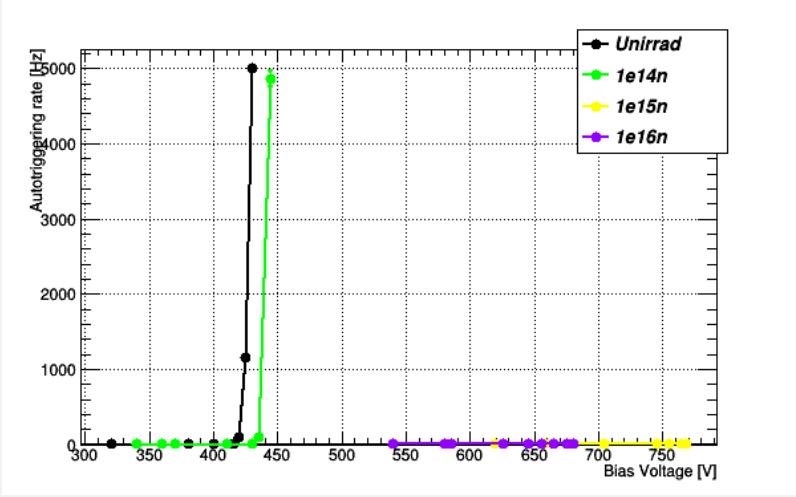
- B+C sensors seems to start auto-triggering before than B and Ga sensors
- Neutron irradiated sensors has lower acceptor removal than proton which leaves more of the gain layer available

CNM Run 12916 AIDA2020



- Unirradiated sensor present a high auto-triggering rate at low voltage which hinders operating it at cold temperature
- Only marginal performances can be achieved before irradiation

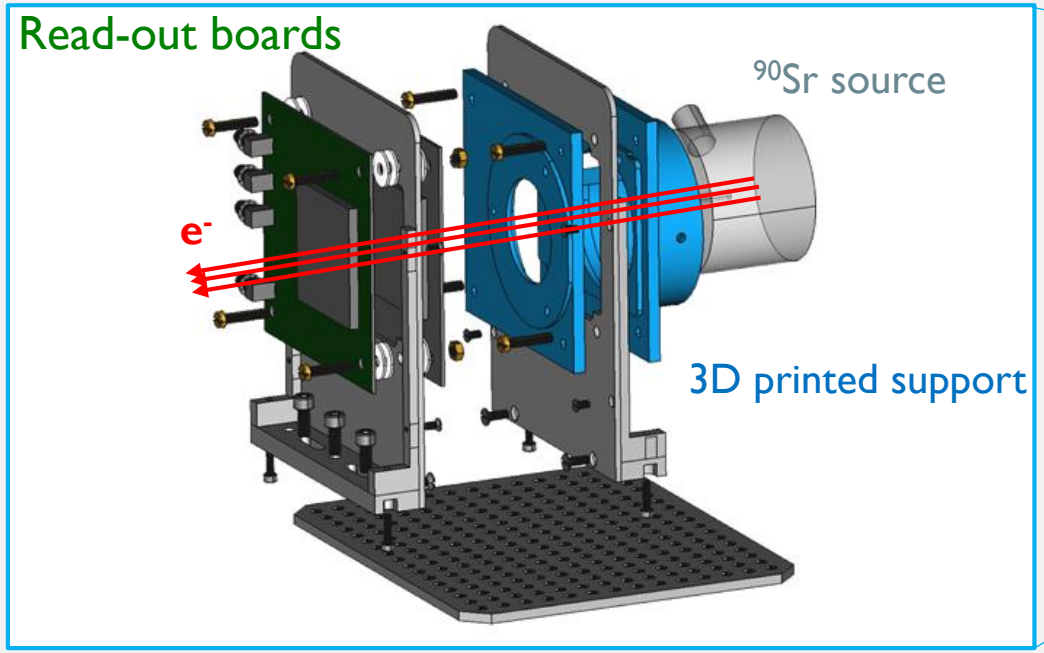
CNM Run 13002 EPI



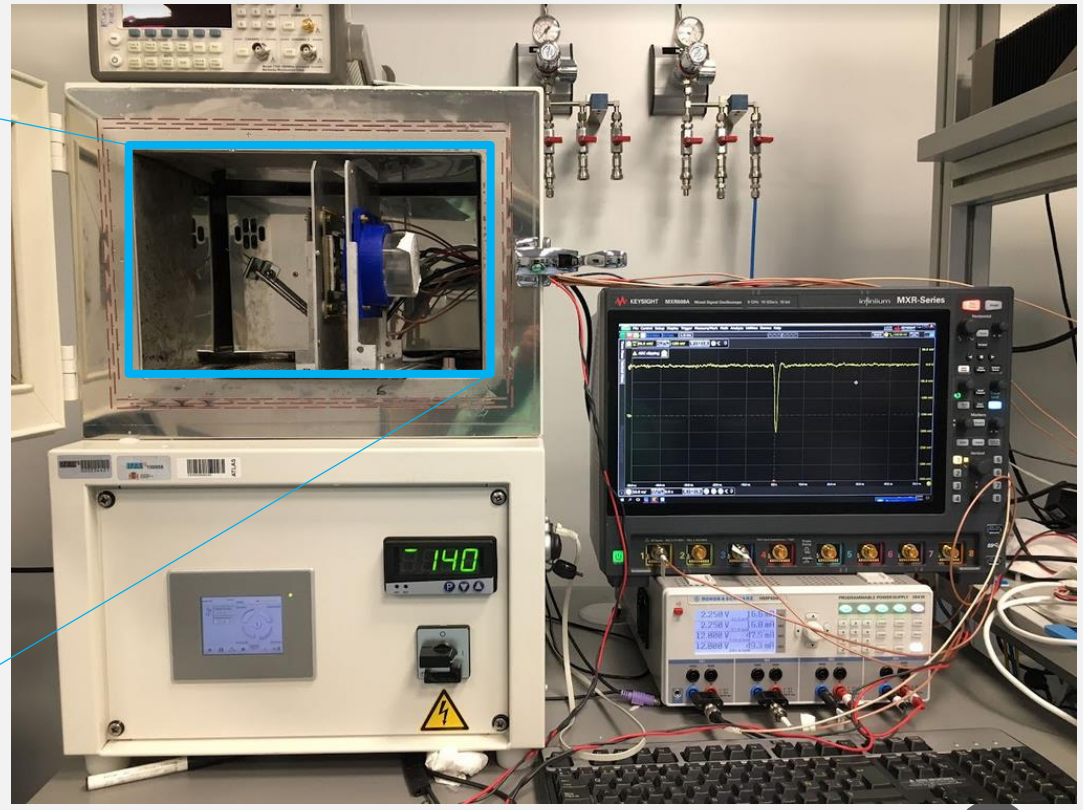
- All the fluences present enough room to operate between V_{gl} and V_{bd}
- No detectable auto-triggering up to 770 V for 10^{15} n_{eq}/cm^2 and up to 720 V for 10^{16} n_{eq}/cm^2 but high current, not possible to go higher in voltage

Charged particle measurements

- **Set-up**
  - ^{90}Sr source, custom read-out boards, oscilloscope
  - Temperature control down to -30 °C with climate chamber
  - Avoid condensation by providing dry air

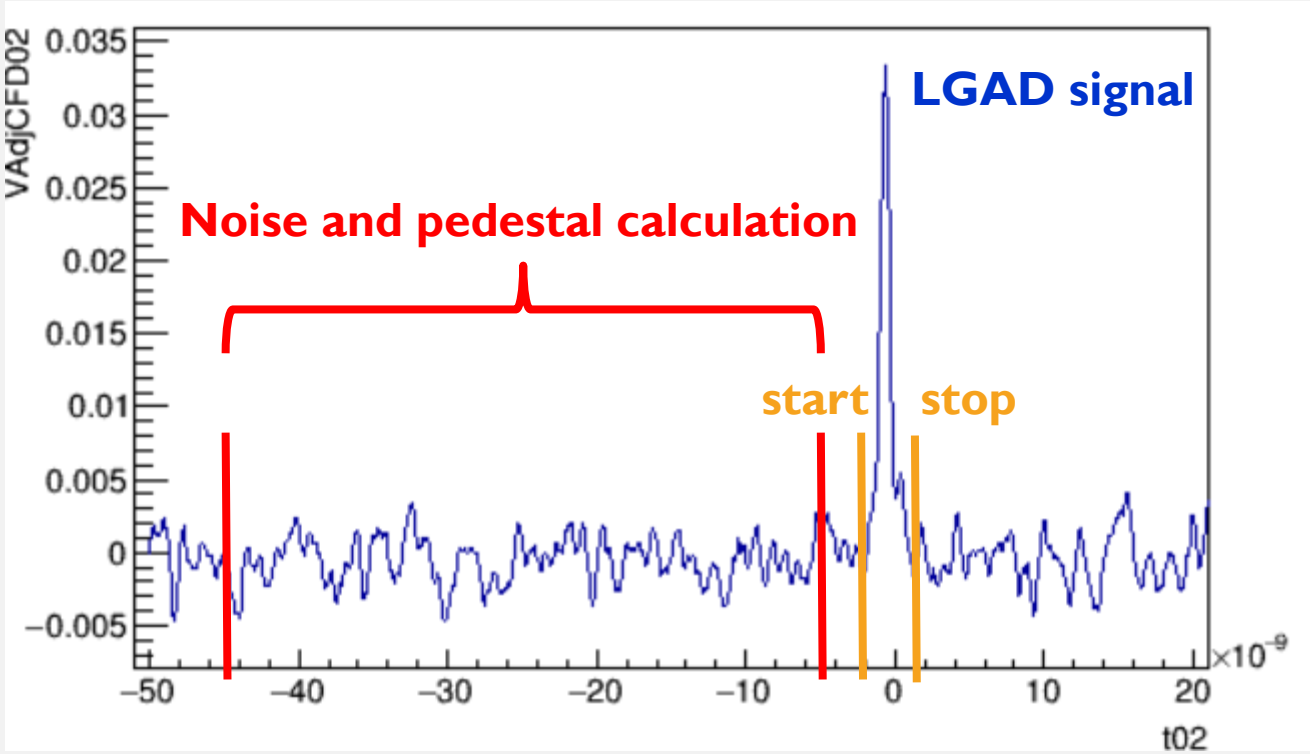


- **Measurements:**
  - Collected charge
  - Time resolution



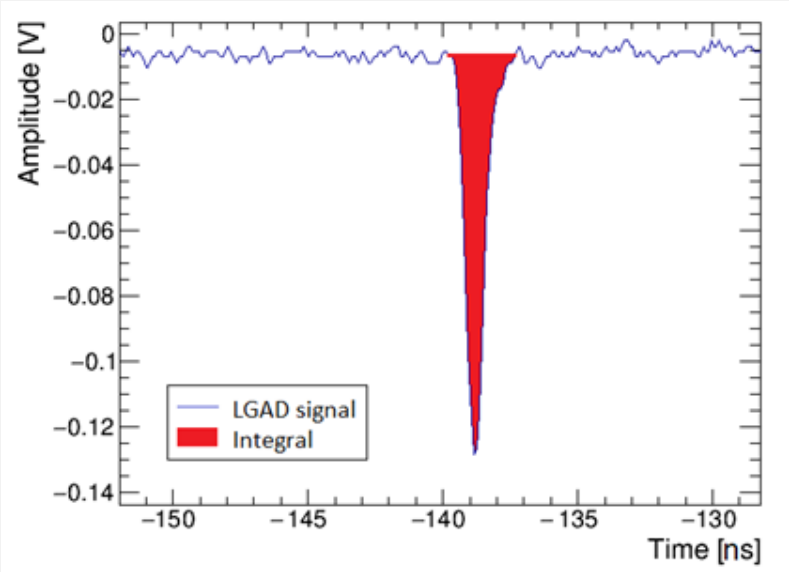
LGAD analysis framework

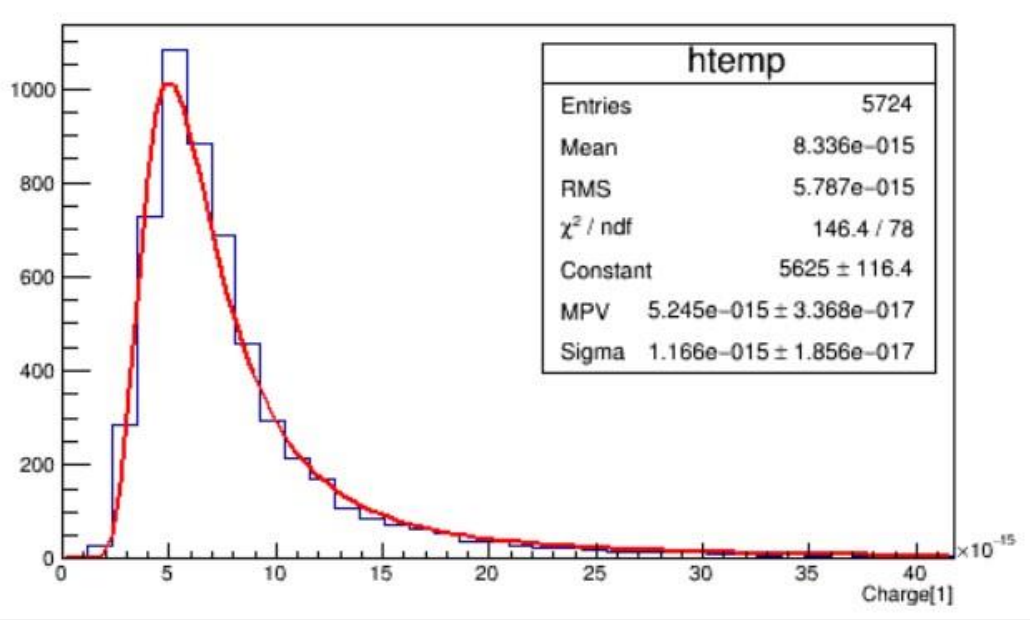
- Waveform processing performed with **LGADUtils framework v1.0 (C++ based)** developed at IFAE by E. L. Gkougkousis (documentation, gitlab)
- Steps:
  - Conversion oscilloscope ASCII/binary data to Root ntuple with raw waveform information
  - Merging with track ntuple from EUTelescope (in test beam)
  - Waveform analysis
    - Determination of pulse polarity, signal start and stop, determine if the pulse is noise or signal
    - Calculate noise level and pedestal using Gaussian fit, pedestal subtraction, re-calculation of start and stop of the signal
    - Compute charge, rise time, time at different CFD fractions, ...
  - User analysis
    - Efficiency
    - Timing



LGAD collected charge

- At each bias voltage point:
  - For each recorded waveform (event), after pedestal substraction, the charge is calculated as the integral of the LGAD signal area
  - A charge distribution is built
  - The collected charge is defined as the MPV value of the Landau-Gauss fit

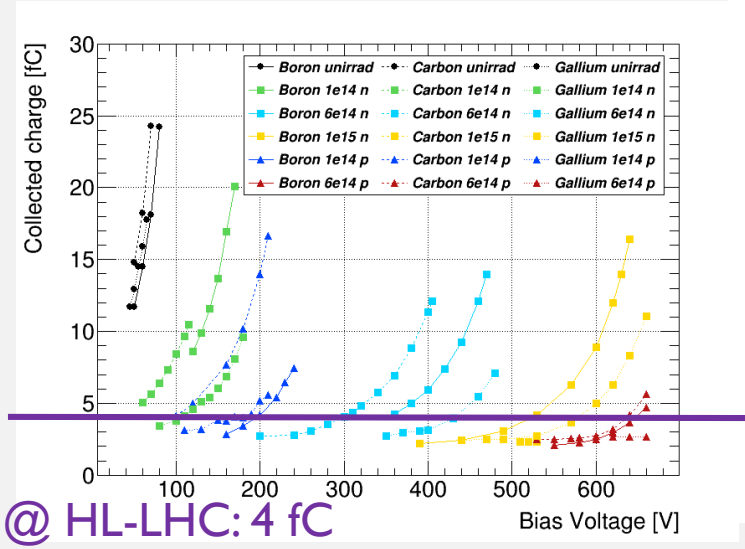




Collected charge

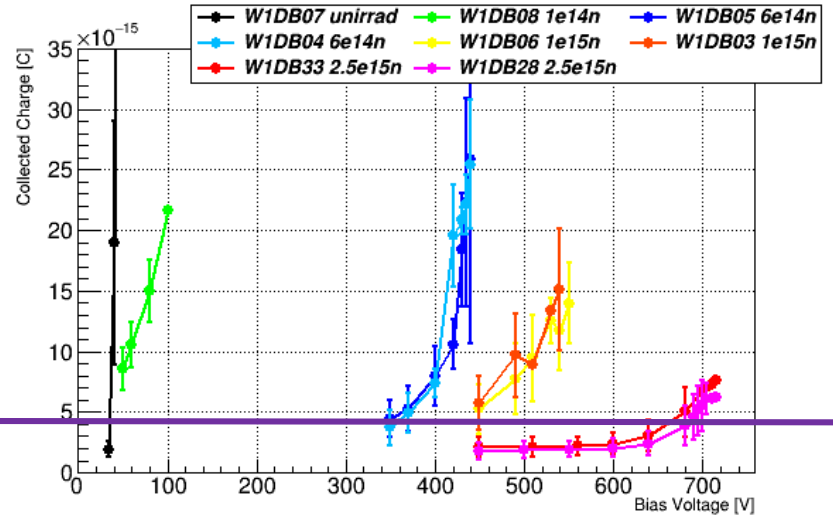
$T = -30°C$

CNM Run 10478 B, B+C, 10924 Ga

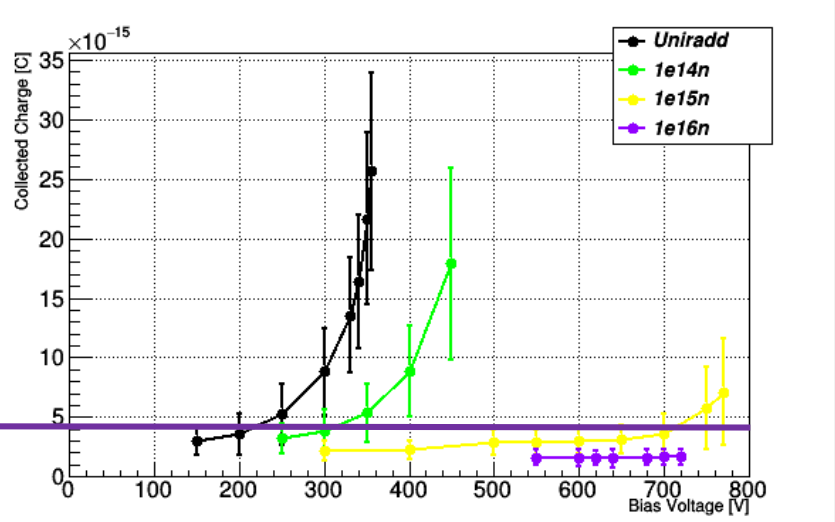


Limit @ HL-LHC: 4 fC

CNM Run 12916 AIDA2020



CNM Run 13002 EPI



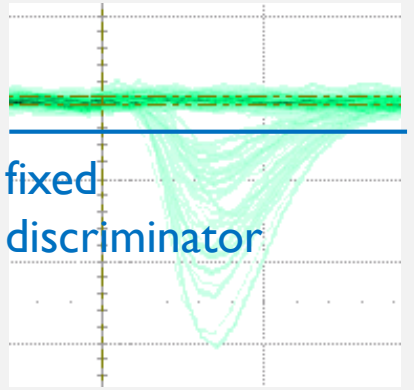
- C sensors have larger charge collection than B and Ga at the same bias voltage
- C helps to diminish the effect of gain reduction with irradiation
- Although B+C sensors start auto-triggering earlier in voltage than other doping
  - This make them not operable at higher voltages

- Unirradiated sensor results are biased by the high auto-triggering rate
  - Not enough room to operate the sensor at -30°C
- 2.5×10^{15} n_{eq}/cm^2 irradiated sensors reach 4 fC for bias voltage higher than 680 V

- Up to 10^{14} n_{eq}/cm^2 irradiated sensors a high collected charge (>10 fC) is achieved
- For 10^{15} n_{eq}/cm^2 irradiated sensor 4 fC is reached at BV>700 V
- No detectable gain for 1e16 n up to 720 V
- Foreseen tests of intermediate fluences (5×10^{14}, 8×10^{14}, 2×10^{15}, 3×10^{15} and 5×10^{15} n_{eq}/cm^2)

- More on gain studies for B, B+C, Ga in Vagelis' talk

LGAD time resolution (ref. LGAD)

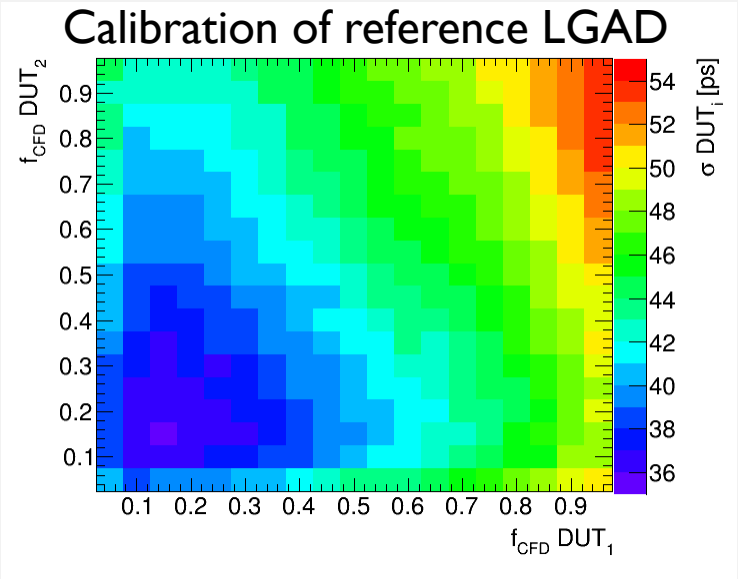


- Time walk effect due to signals with different amplitude reaching a single discriminator threshold is corrected using Constant Fraction Discrimination (CFD) method

- Find optimal CFD fraction achieving the minimum time resolution for the reference LGAD
  - Build a 2D map of time resolution as a function of the CFD fractions ($f_{CFD_{DUT1}}$, $f_{CFD_{DUT2}}$)
    - Time difference distribution calculated as:

$$\Delta t = t_{DUT1(f_{CFD_i})} - t_{DUT2(f_{CFD_j})}$$

    - Time resolution is defined as $^{1}/_{\sqrt{2}}$ the standard deviation of the Gaussian fit



- Reference LGAD calibrated in the lab at -30 °C
  - Best time resolution achieved is 35.7 ps for $f_{CFD_{ref}}$=15%

LGAD time resolution (DUT)

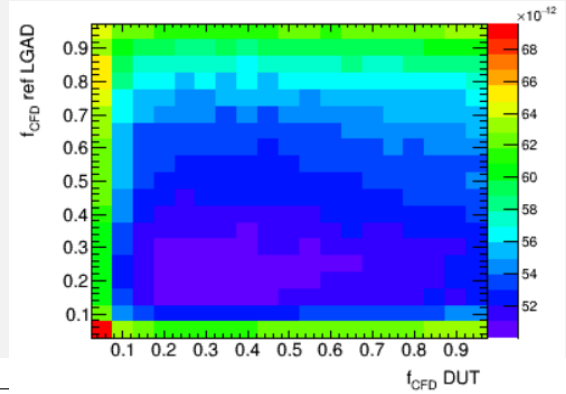
- Find optimal CFD fraction achieving the minimum time resolution for the DUT
  - Build a 2D map of time resolution as a function of the CFD fractions ($f_{CFD_{DUT}}$, $f_{CFD_{ref\ LGAD}}$)
    - Time difference distribution calculated as:

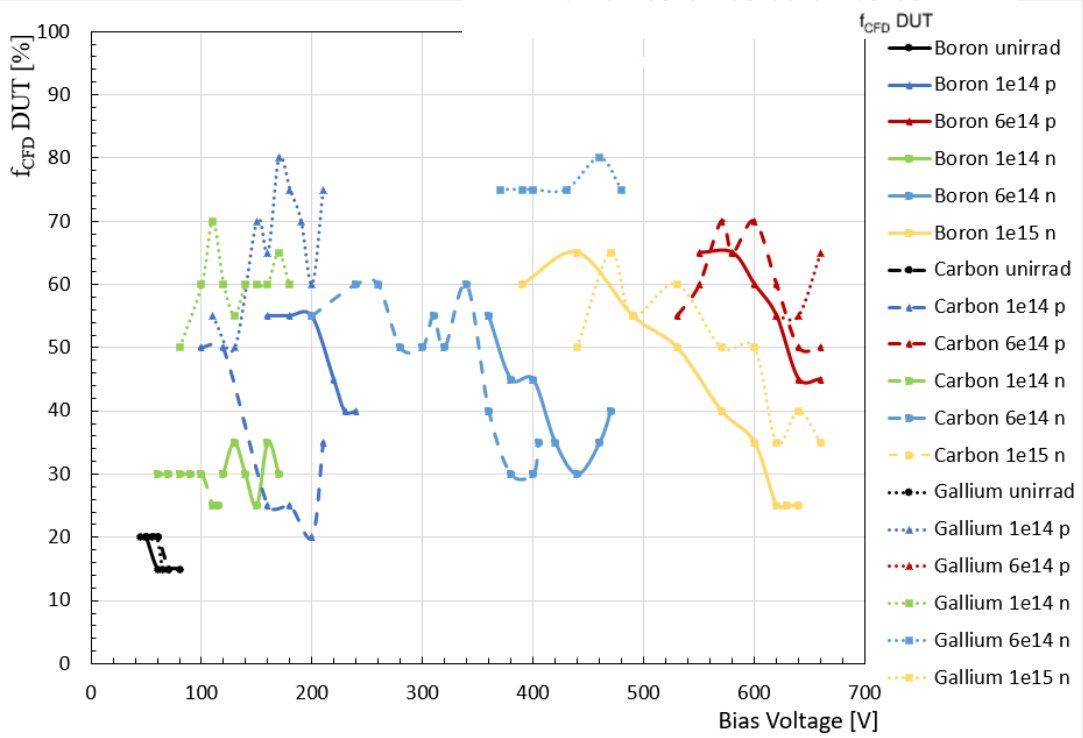
$$\Delta t = t_{DUT(f_{CFD_i})} - t_{ref\ LGAD(f_{CFD_j})}$$

    - Time resolution is defined as:

$$\sigma_{DUT} = \sqrt{\sigma_{fit}^2 - \sigma_{ref\ LGAD}^2}$$

  - Fraction defined by the dominant contribution
    - Unirradiated sensor → Landau fluctuations of charge deposition
    - Irradiated sensor → jitter (higher threshold)

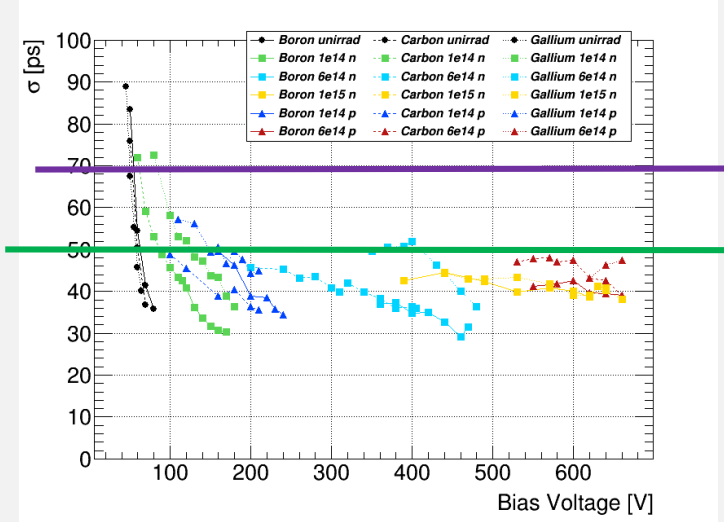




Time resolution

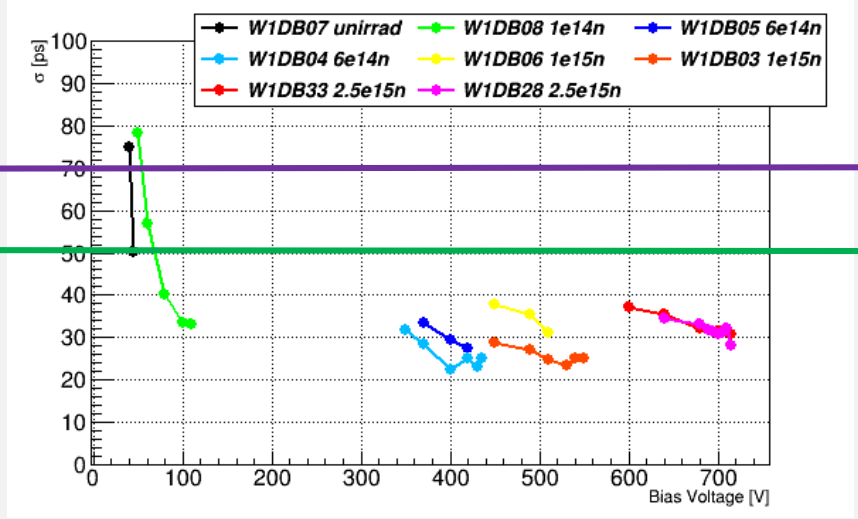
$T = -30°C$

CNM Run 10478 B, B+C, 10924 Ga



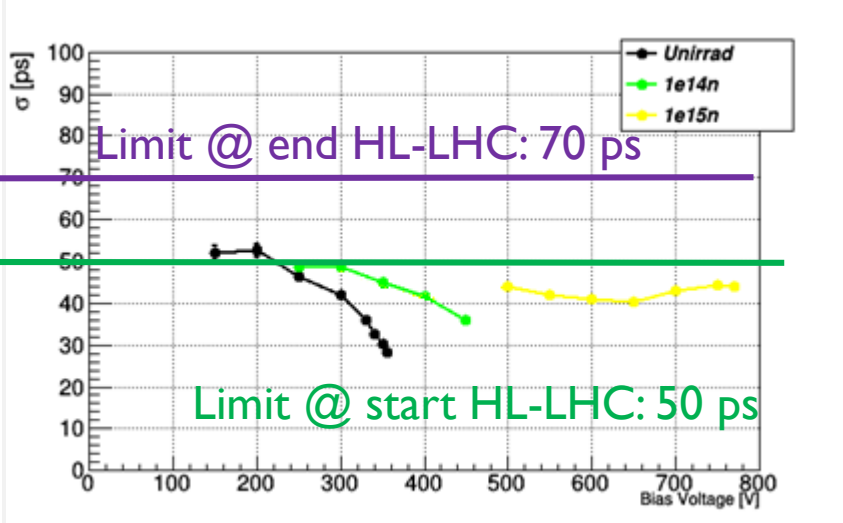
- Achieved time resolution better than 50 ps
- B and B+C are similar in time performances
- Ga achieves a worse time resolution due to the high leakage current

CNM Run 12916 AIDA2020



- Unirradiated sensor cannot be operate at higher voltage due to auto-triggering, marginal performances in timing
- Irradiated sensors achieve a time resolution lower than 40 ps at all level of neutron irradiation

CNM Run 13002 EPI

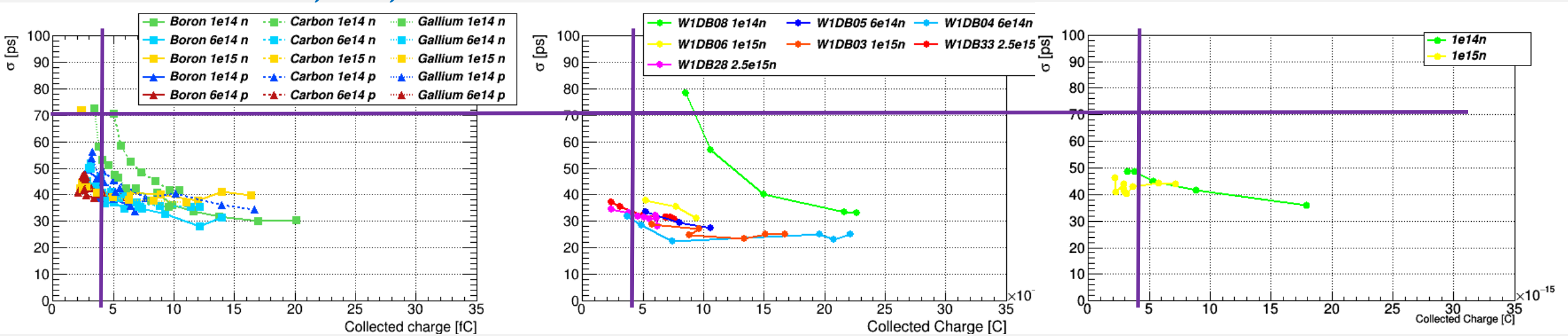


- A time resolution < 50 ps is achieved for sensor irradiated up to 10^{15} n_{eq}/cm^2
  - A plateau-like around 43 ps is reached for this fluence
- For 10^{14} n_{eq}/cm^2 the measured time resolution is below 40 ps

Time resolution vs Collected charge

$T = -30°C$

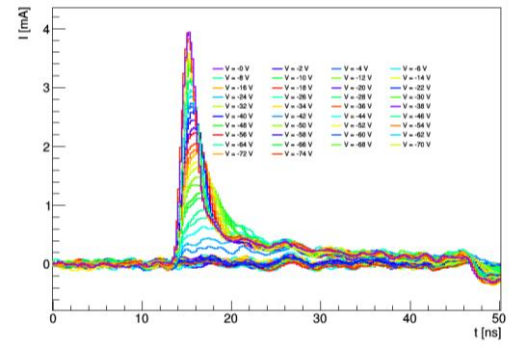
CNM Run 10478 B, B+C, 10924 Ga **CNM Run 12916 AIDA2020** **CNM Run 13002 EPI**

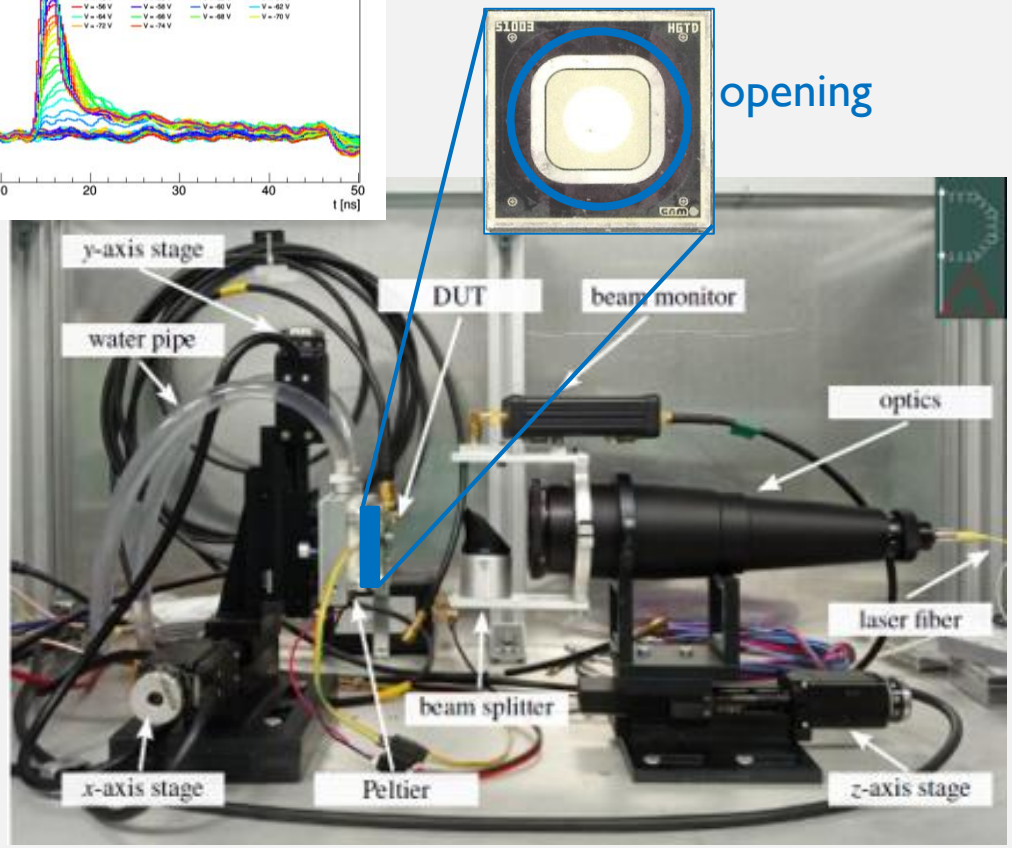


- LGADs exposed to neutron fluence up to 2.5×10^{15} n_{eq}/cm^2 and to proton fluence up to 6×10^{14} n_{eq}/cm^2
- A charge of 4 fC can be reach up to a fluence of 2.5×10^{15} n_{eq}/cm^2, providing a time resolution better than 70 ps per hit
- The performance of LGADs from all three technologies is similar
- The time resolution for the largest fluence is fully dominated by the electronics jitter

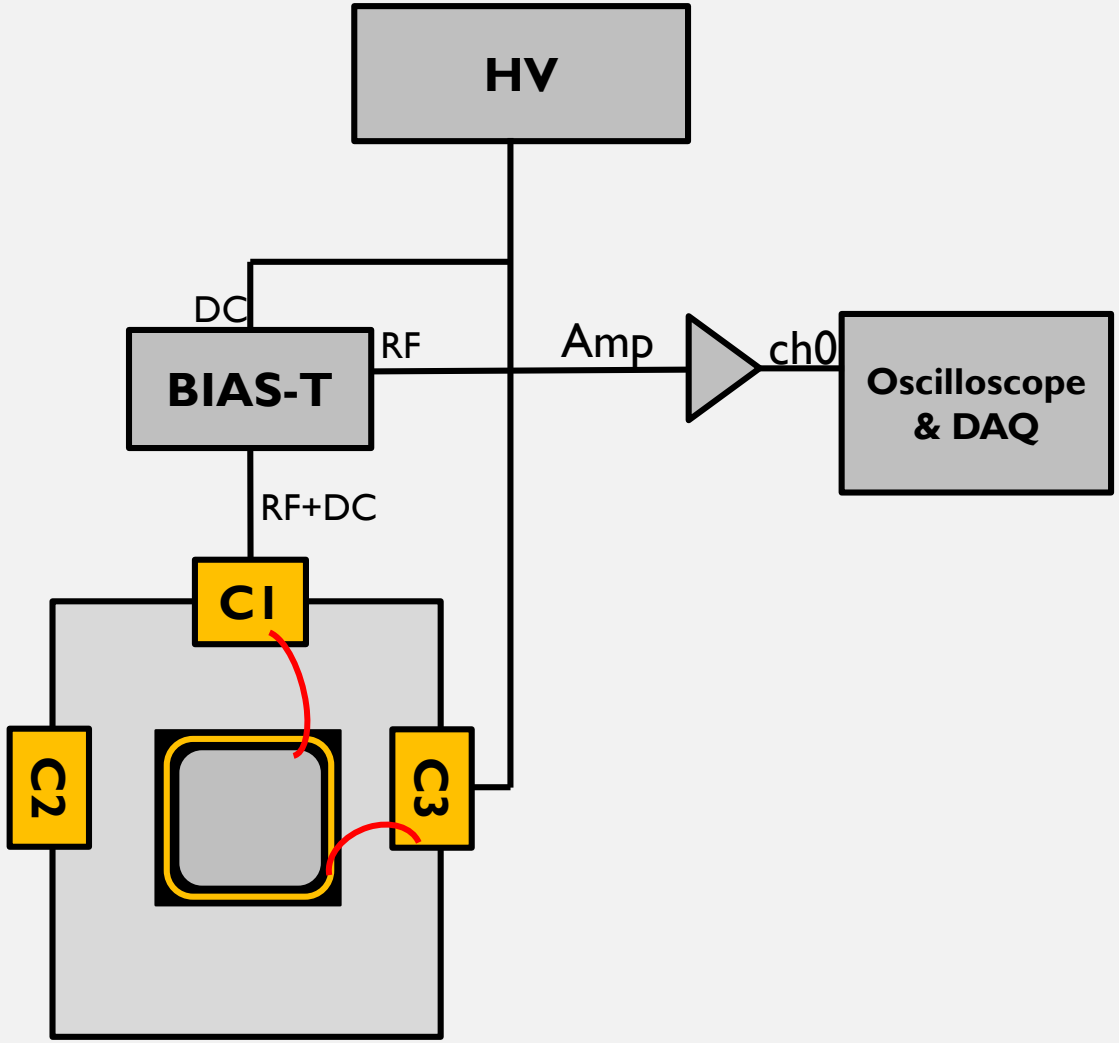
Transient Current Technique (TCT)

- **Set-up:**
  - Time-resolved current waveforms introduced by drift charge inside a sensor
  - Current proportional to the number of charges, drift velocity and weighting field of the readout electrode
  - Pulsed laser source (spot size = 10 μm) mimics the behavior of a charged particle
    - Red ($\lambda_1 = 640\ nm$) and Infra-Red ($\lambda_2 = 1040\ nm$)
  - Possibility to perform room temperature and cold measurements (till -20 °C)
    - Cooling system with Peltier + Chiller
    - Dry environment
  - LGAD assembled in a metal box mounted on the movable X-Y stage
  - Set-up is remotely controlled
  - Detector illuminated from the back with IR laser
    - To perform TCT LGADs need to have an opening in the metallization layer
- **Aim of measurements:**
  - Compare behaviour before and after irradiation
    - Gain for single pad devices
    - IP gap for 2×2 arrays





Schematic and read-out: single pad

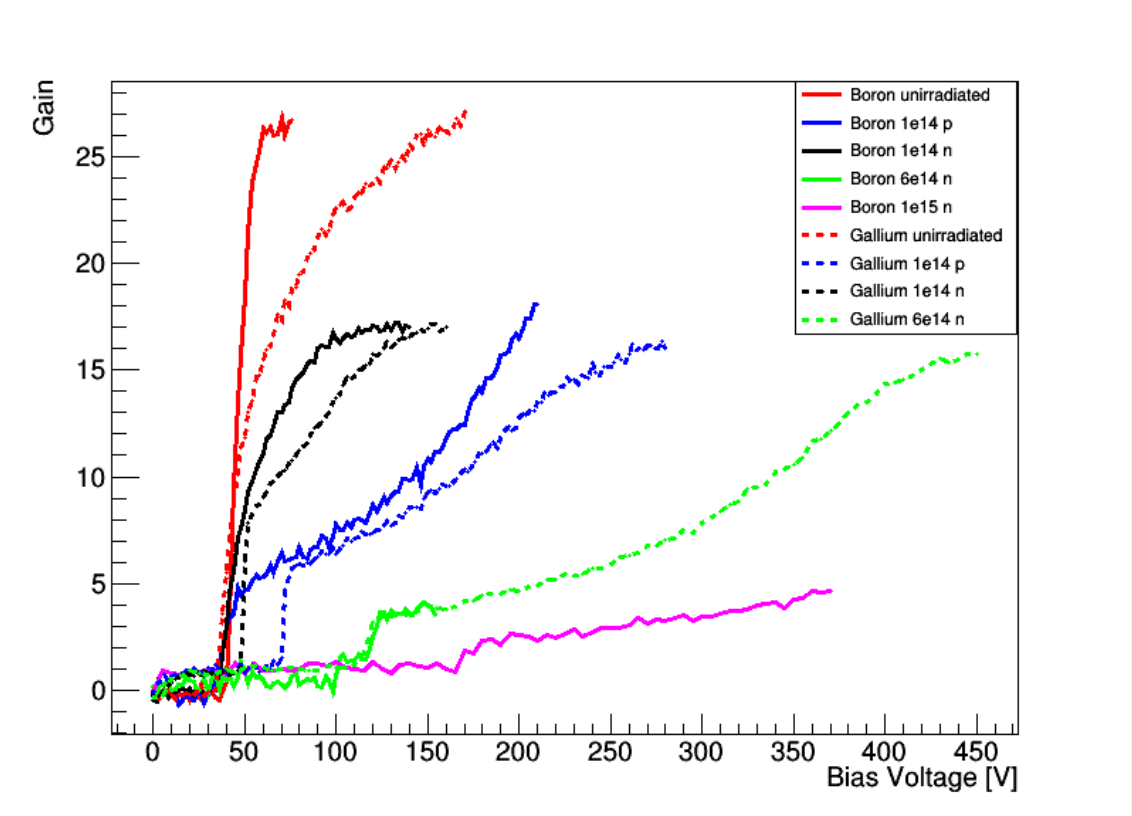


- Sensor is biased from the top side with POSITIVE voltage, this is possible due to the presence of the BIAS-T element
  - DC input is used for bias voltage
  - RF output is sent to amplifier and then to the scope
  - RF+DC in/out is used for the connection with the sensor
- Illuminated with IR lased on the backside
- CIVIDEC amplifiers present a gain of 100
- Average of 1000 waveforms are collected from DRS oscilloscope

B and Ga results: Gain

$T = -20°C$

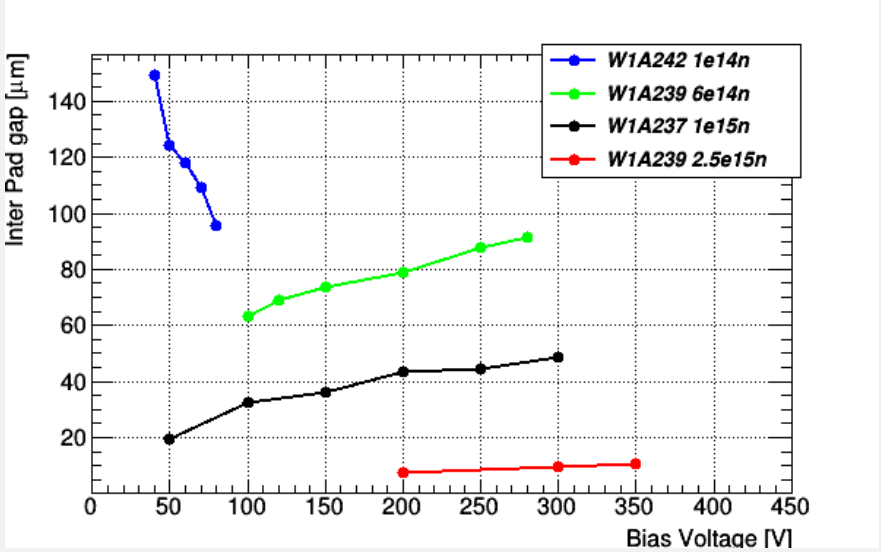
- Measurements for B and Ga doped LGADs up to 10^{15}
  - p and n irradiation
  - B+C LGADs metalized on the back, no possibility to measure them
- Infra-Red laser shot on the back of the sensor
- Gain is computed as: $G = \frac{Q_{DUT}}{<Q_{pin}>}$ for each bias voltage point
  - Q_{DUT} is the collected charge obtained by the integration of waveform signal on the DUT
  - $< Q_{pin} >$ is the averaged collected charge obtained for the device with no multiplication (PIN) with the same size
- Boron LGADs show more gain than Gallium ones at the same bias voltages, in agreement with beta source results



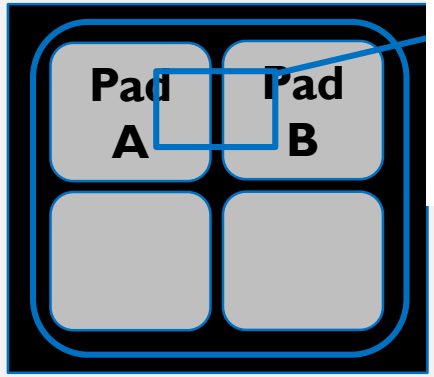
AIDA2020 results: IP gap

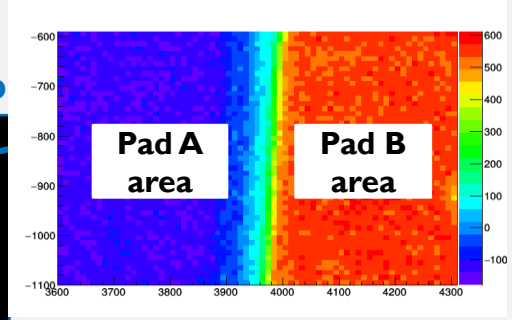
$T = -20°C$

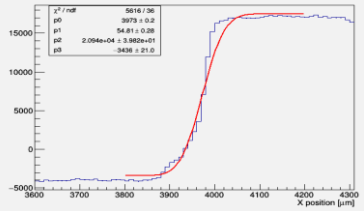
- Measure IP gap by scanning the area between two pads
  - Record 1k waveforms for each X-Y position
  - Pad A and B are readout through two different lines
  - Build a 2D map of collected charge as a function of the laser position
  - Make projection for each pad and fit it with an S-curve
  - IP is defined as: $IP\ gap = |x_{A\ 50\%} - x_{B\ 50\%}|$



Scanned area for IP gap





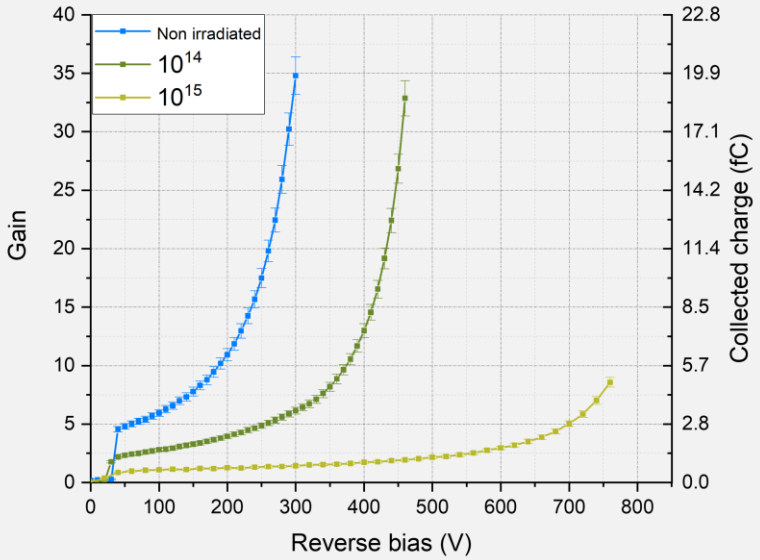


- Unirradiated sensor not operable →high current and early breakdown
- Low fluences
  - Carriers generated underneath the gain layer end their drift on JTE and don't undergo multiplication
- High fluences (>6×10^{14} n_{eq}/cm^2):
  - Some gain from carriers drifting to the JTE, a smaller IP has been measured
  - The IP gap is larger at higher bias voltages
- Results are compatible with previous results on LGADs from other vendors (slides@38th RD50 Workshop) and in agreement with their simulation

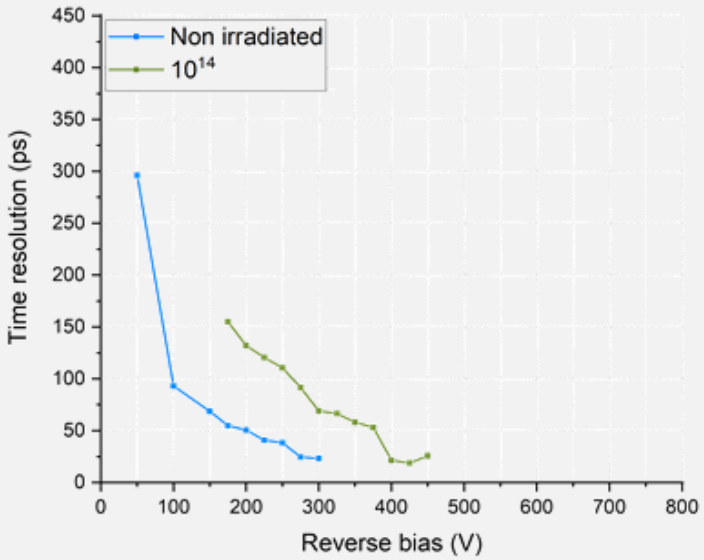
Epi results: Gain and time resolution

$T = -20°C$

Gain



Time resolution



- Gain is computed as: $G = \frac{Q_{DUT}}{<Q_{pin}>}$ for each bias voltage point
  - Q_{DUT} is the collected charge obtained by the integral of the signal from the DUT
  - $< Q_{pin} >$ is the average collected charge obtained for the device with no multiplication (PIN)
- Gain 1 = 0.569 fC
  - MIP → 67 e/h pairs/μm in silicon low doped x 53 μm

- Laser signal is split, one is delayed by 50 ns and then both are combined
- Time difference is calculated at different CFD fractions for 1000 events for each voltage point
- Intrinsic time resolution of the LGAD is $\sigma_{DUT} = \frac{\sigma_{fit}}{\sqrt{2}}$
- Minimum time resolution as a function of the reverse bias
- Results aready presented to RD50 community: [slides@38th RD50 Workshop]

Summary and outlook

- **Boron, Boron + Carbon and Gallium doping (Run 10478 W4 & W5, Run 10924 W6)**
  - **Carbon** seems to help to maintain gain after irradiation
    - However, in this first run with Carbon, we suspect it was diffused out of the multiplication layer and the benefits are not clear
    - But good control of C implantation critical
  - **Gallium** presents 20% less gain and acceptor removal wrt Boron, but requires better diffusion techniques
    - Ga disfavoured due to poorer radiation hardness and timing performances
  - LGADs have been also tested in test beams (2018-2019) and a paper with results is in preparation
- **AIDA 2020 Boron (Run 12916)**
  - Unirradiated LGAD does not show enough room to operate between V_{gl}, V_{fd} and V_{bd} voltages and early breakdown
  - Good performances in collected charge and time resolution achieved for fluences up to 2.5×10^{15} n_{eq}/cm^2
- **Epitaxial Boron (Run 13002)**
  - Unirradiated LGADs show enough room to operate between V_{gl}, V_{fd} and V_{bd} voltages and low auto-triggering rate
  - LGADs irradiated to a fluence of 10^{15} n_{eq}/cm^2 work but at relative high bias (700 V), due to low gain and low resistivity of wafer
- **Next steps**
  - A new common ATLAS/CMS run will be ready by the end of this year
    - Epitaxial run with C implanted in the gain layer on some wafers

THANK YOU FOR YOUR ATTENTION

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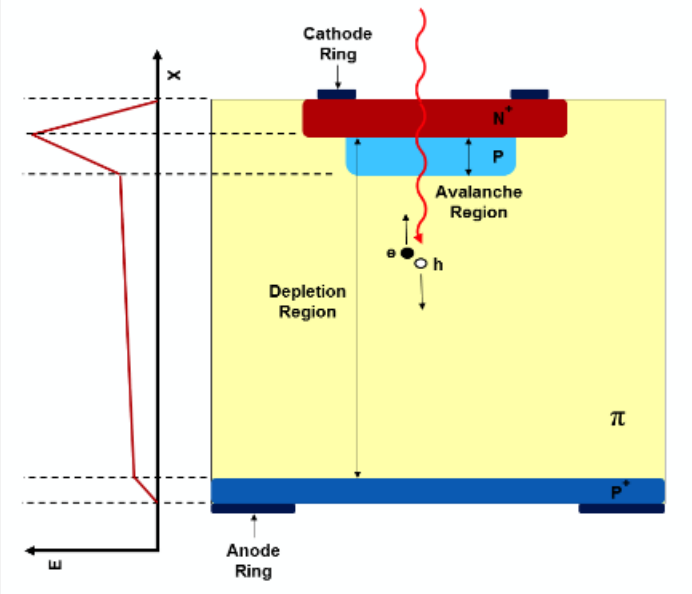
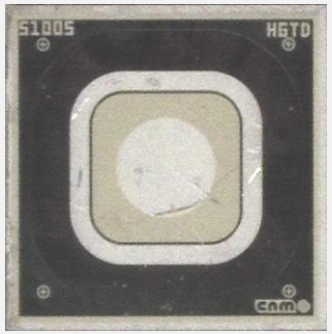
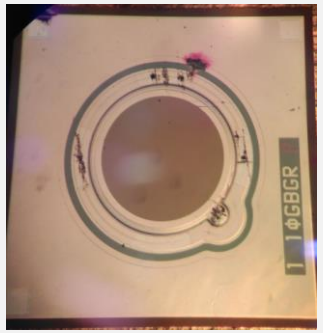
Detection technology: LGAD

- **L**ow **G**ain **A**valanche **D**etectors (LGADs) originally developed by CNM
  - n-p silicon planar detector + multiplication layer that amplifies the signal
  - High E field
  - Moderate internal gain (10-50)
  - Typical rise time 0.5 ns
  - Excellent time resolution <30 ps before irradiation
- R&D programme to deliver thin sensors to provide the required time resolution (30 ps per track), fine segmentation, radiation hardness
  - New doping materials, substrates and new geometries
  - Prototypes tested from CNM, HPK, BNL, FBK





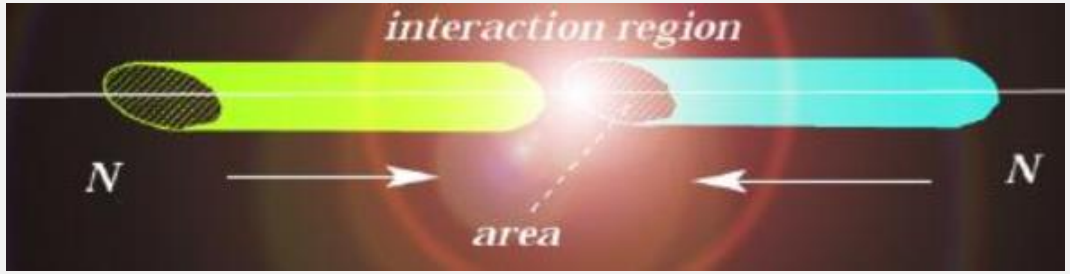
CNM LGAD for HGTD

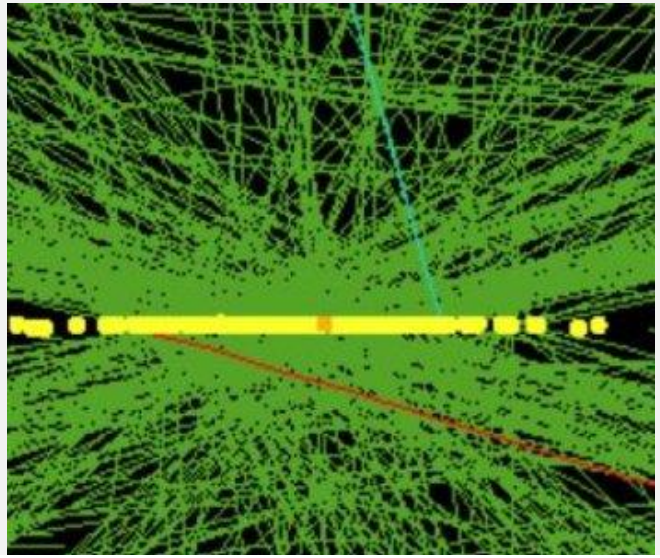


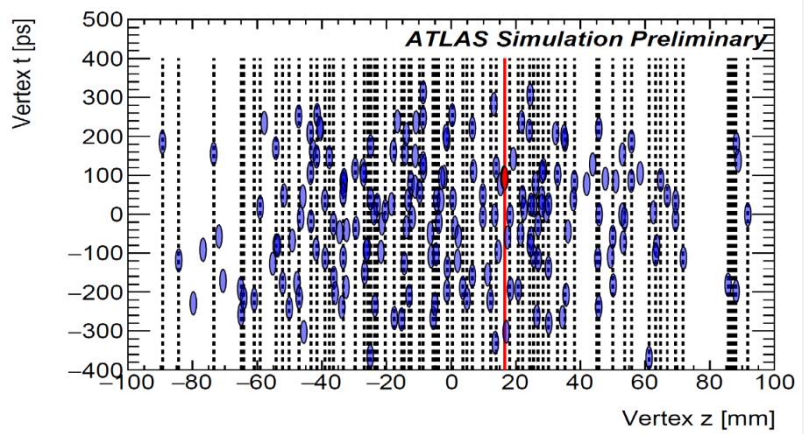
HPK LGAD for HGTD

Why timing is so important?

- **High-Luminosity phase of LHC** (HL-LHC)
  - Instantaneous luminosities up to L ≃ 7.5×10^{34} cm^{-2} s^{-1} (×5 current L_{inst})
    - Luminosity = number of collisions in a detector per cm^2 and per second



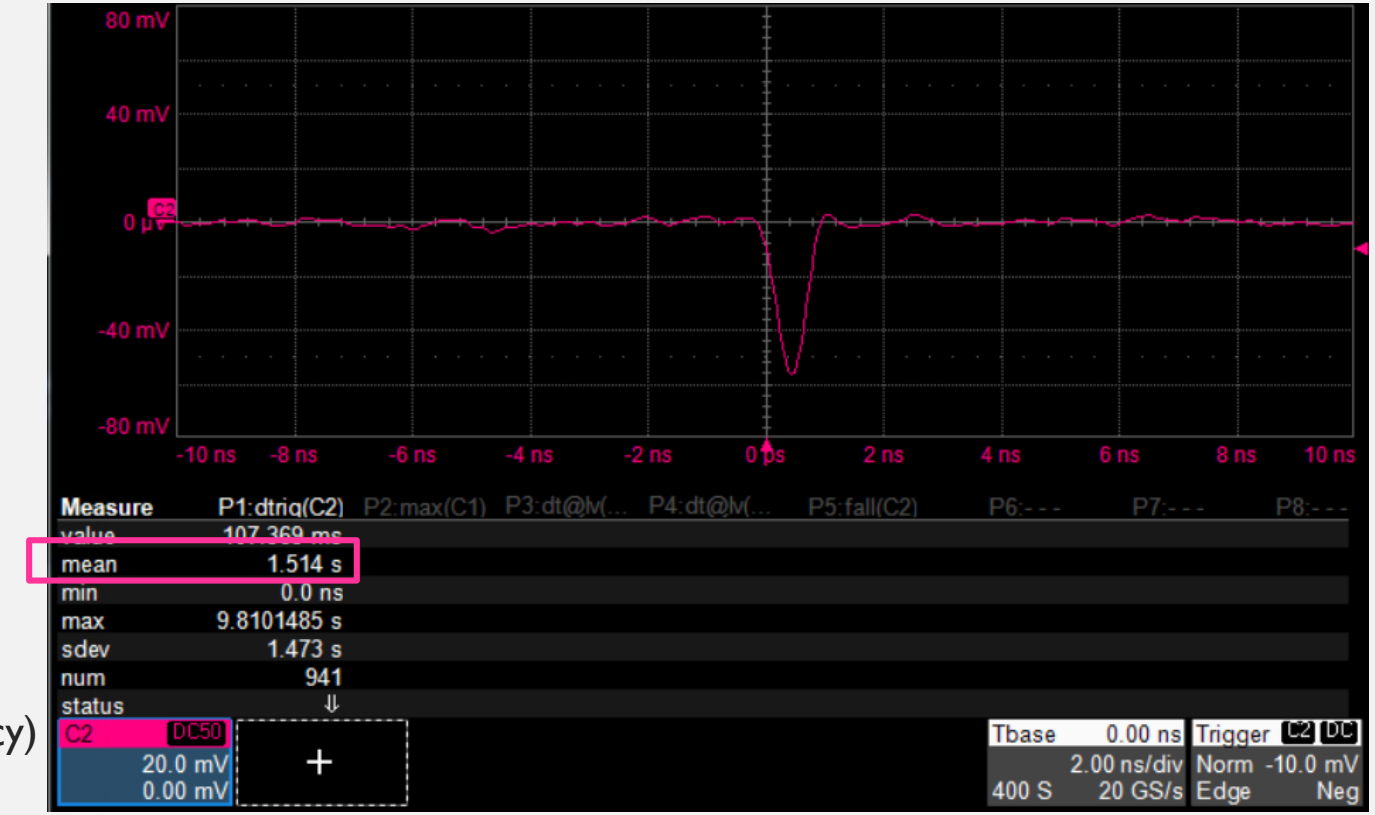




  - Pile-up: $<\mu>$ = 200 interactions per bunch crossing → 1.5 vertex/mm on average
  - Vertex reconstruction and physics objects performance will be significantly degraded
  - Push to higher luminosity → timing is more and more important
    - Using timing information easier to reconstruct vertices

Basic principles

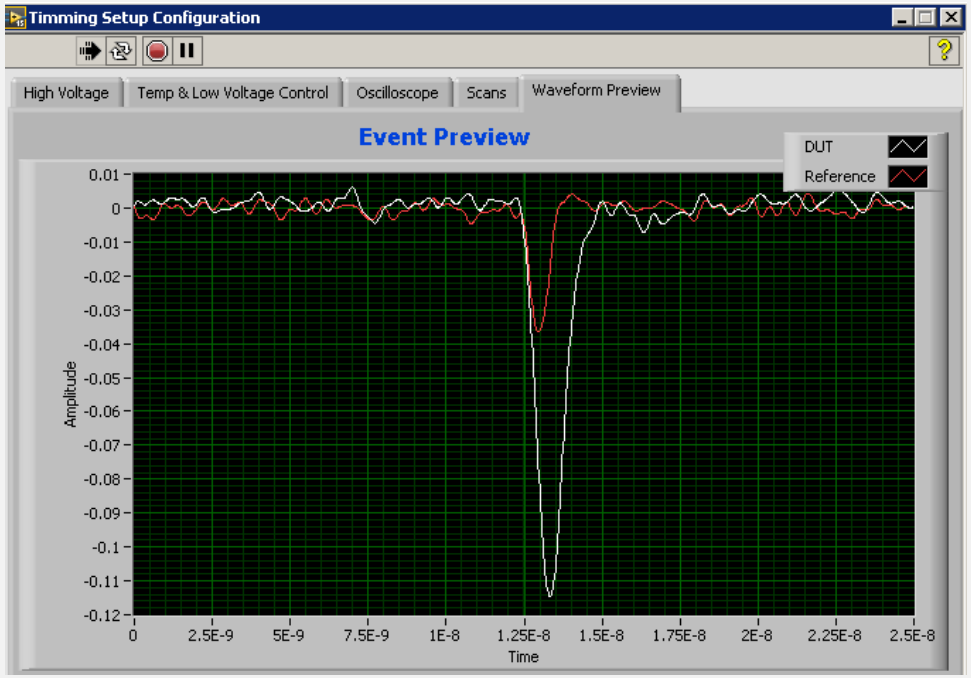
- Study on proton and neutron irradiated CNM LGADs
  - Boron implanted (R10478W4)
  - Boron implanted + Carbon enriched (R10478W5)
  - Gallium implanted (R10924W6)
- We need to make sure that a coincidence event from both tested sensors is a real one, not a fake → need to ensure sensor is not auto-triggering
- Trigger on different threshold values for different bias Voltages (here only showing 10mV)
- No radioactive source or other source of events
- Collect at least 1k events and estimate period (frequency)
- Noise events have waveforms that are identical to real events

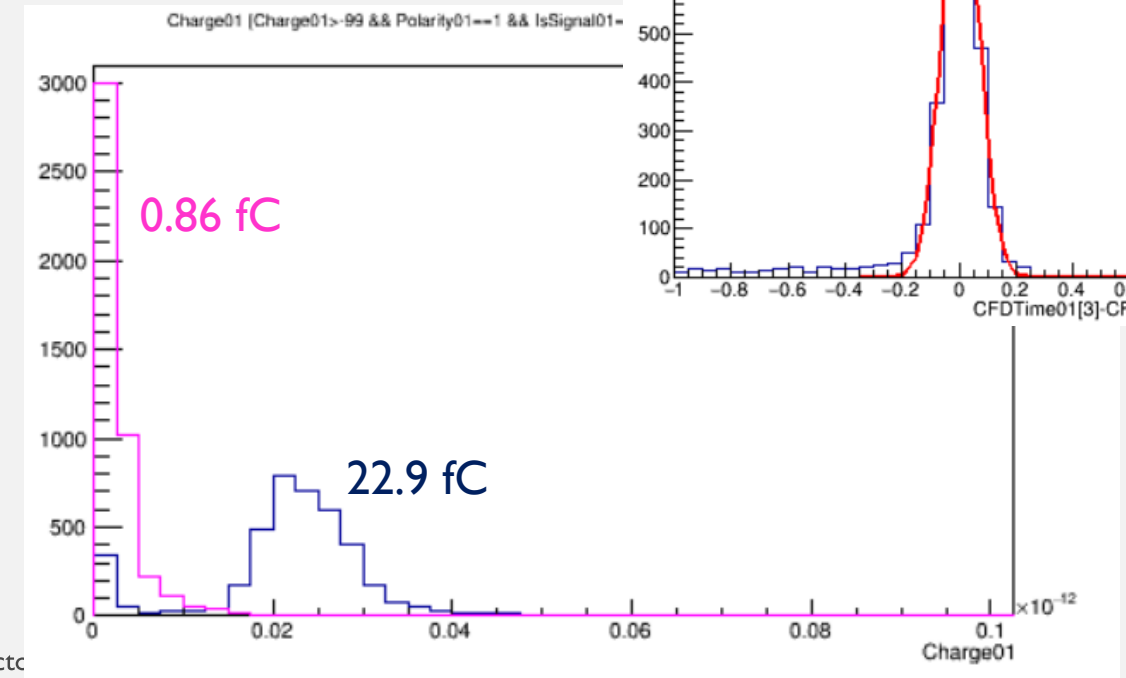


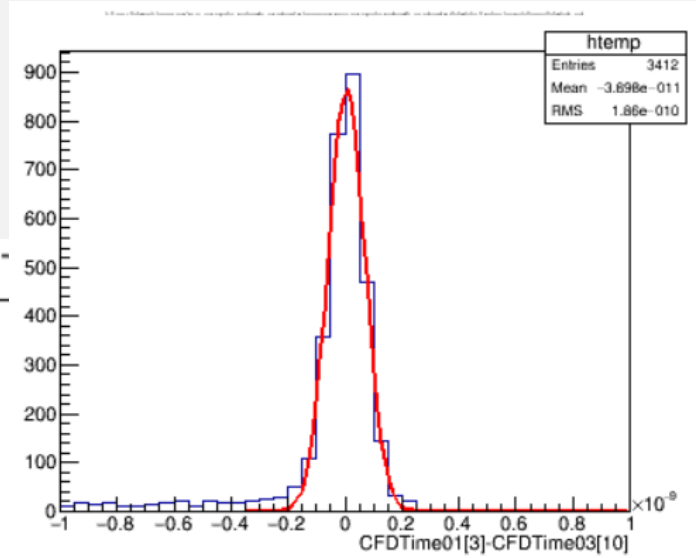
Preliminary results

- Beta source set-up
  - DUT: W6S1080 6e14 p @-560 V (-30 C) → data taking until -700 V
  - Ref: W4S1022 unirradiated @-80 V (-30 C)

σ_{DUT} =64.8 ps (σ_{ref} =35.7 ps) → 54.1 ps



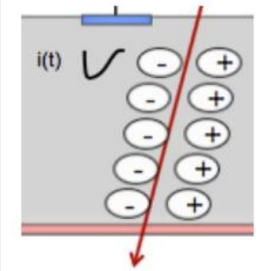


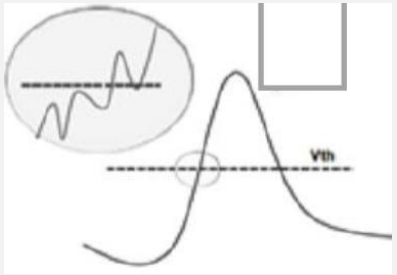


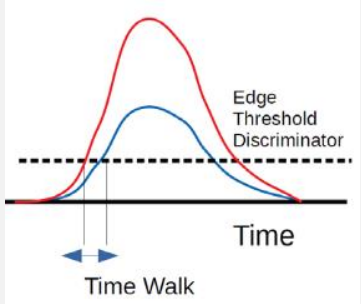
Contributions to timing

- **Time resolution:**
  - Landau term <25 ps
    - Reduce for thin sensors: 35-50 μm
  - Jitter term <15 ps and time walk term <10 ps
    - Low noise and fast signals
  - Digitization granularity ~5 ps
  - Clock distribution <15 ps

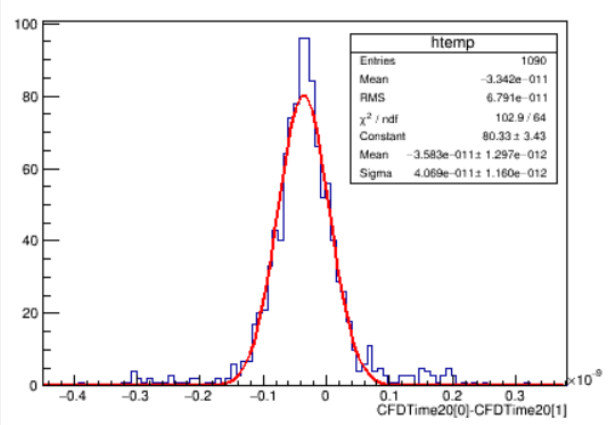
$$\sigma_{tot}^2 = \sigma_{Landau}^2 + \left(\frac{t_{rise}}{S/N}\right)^2 + \left(\left[\frac{V_{thr}}{S/t_{rise}}\right]_{RMS}\right)^2 + \left(\frac{\mathrm{TDC}_{bin}}{\sqrt{12}}\right)^2 + \sigma_{clock}^2$$

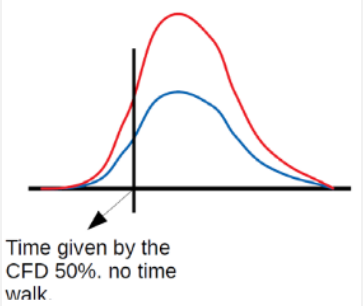






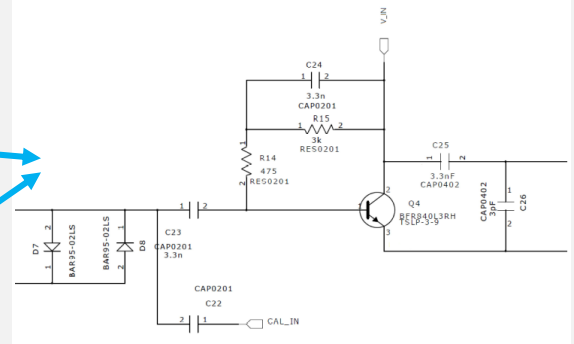
- Time walk corrections on beam test data using the **C**onstant **F**raction **D**iscriminator (CFD) technique
  - Considering the time at a fraction of 50% of the amplitude (typical fraction is 20%)

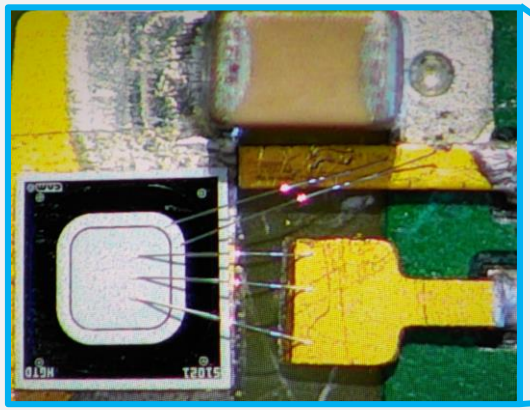


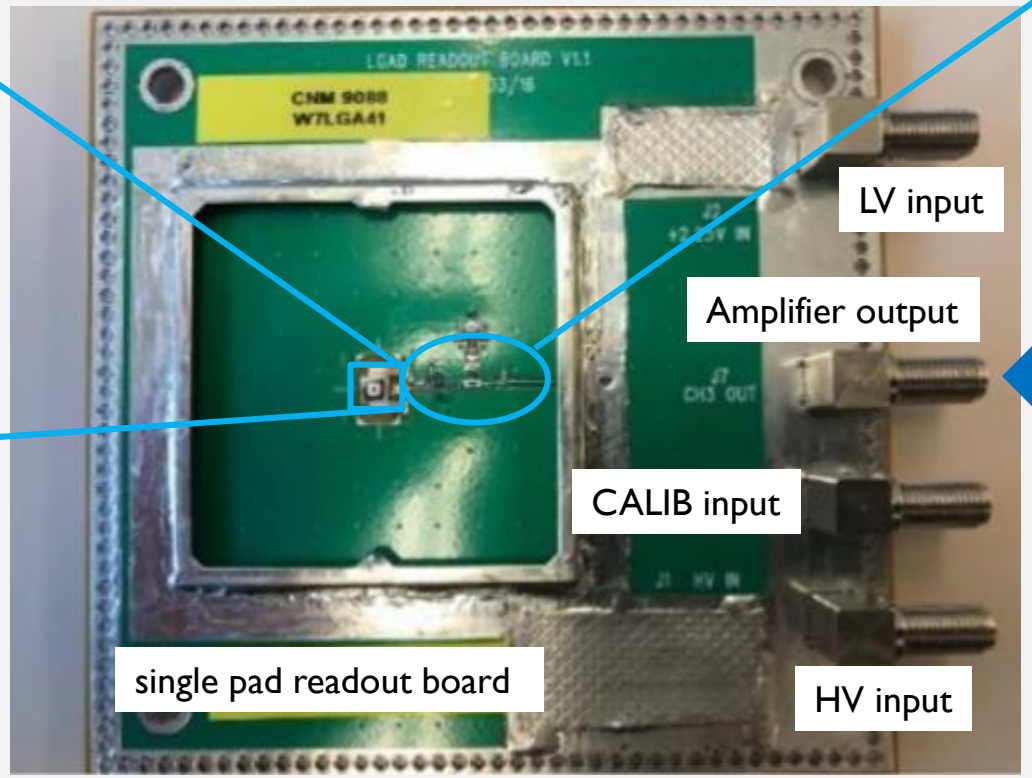


Assembly Sensor + Readout board

- 50 sensors (unirradiated, p- and n-irradiated) tested so far
- LGAD readout boards with trans-impedance first stage amplifier
- Voltage second stage amplifiers with hermetic E/B cover design





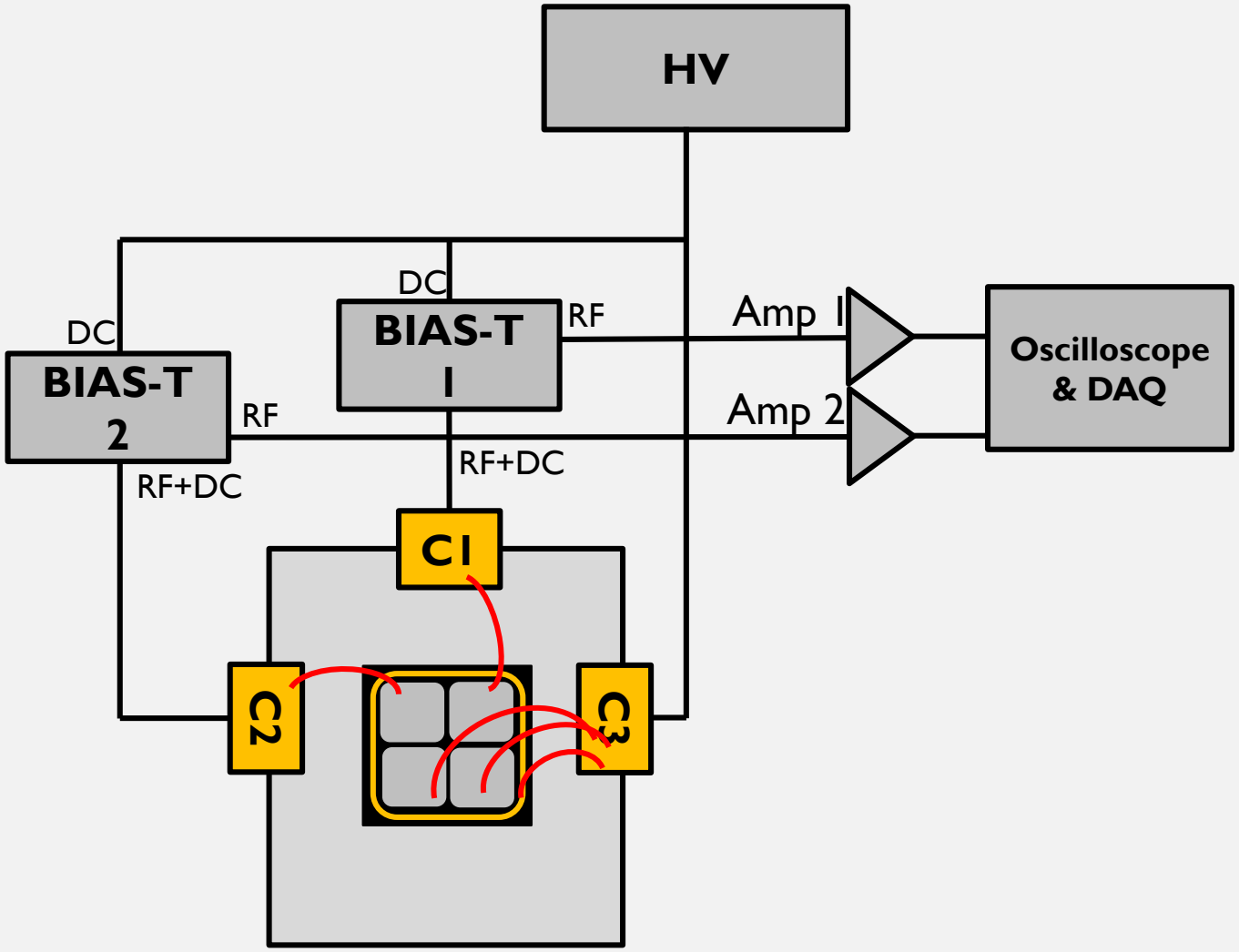


Second stage amplifier output to oscilloscope

- Sensor attached to board using double-sided conductive tape
- Amplifier input coupled to metallization layer via wire bonds
- Guard ring grounded

- Gain of ~10
- 2 GHz Bandwidth

Schematic and read-out: 2x2 arrays



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  - DC input is used for bias voltage
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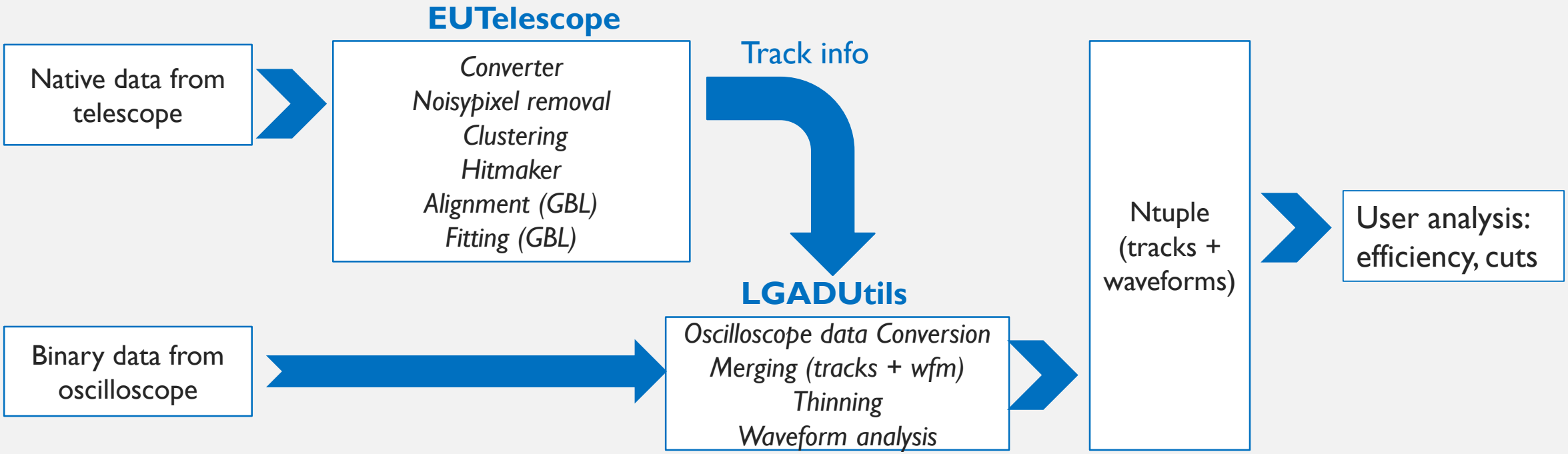
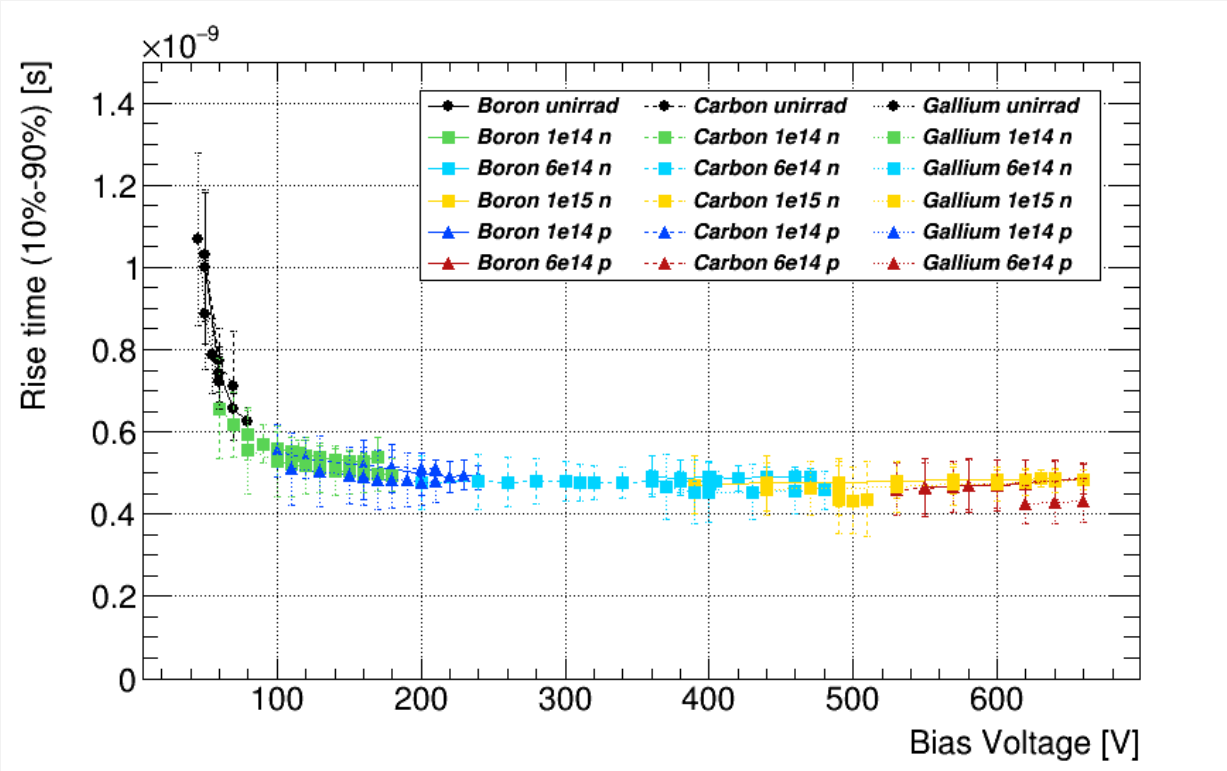
  - RF+DC in/out is used for the connection with the sensor
- Illuminated with IR lased on the backside
- CIVIDEC amplifiers present a gain of 100
- Average of 1000 waveforms are collected from DRS oscilloscope

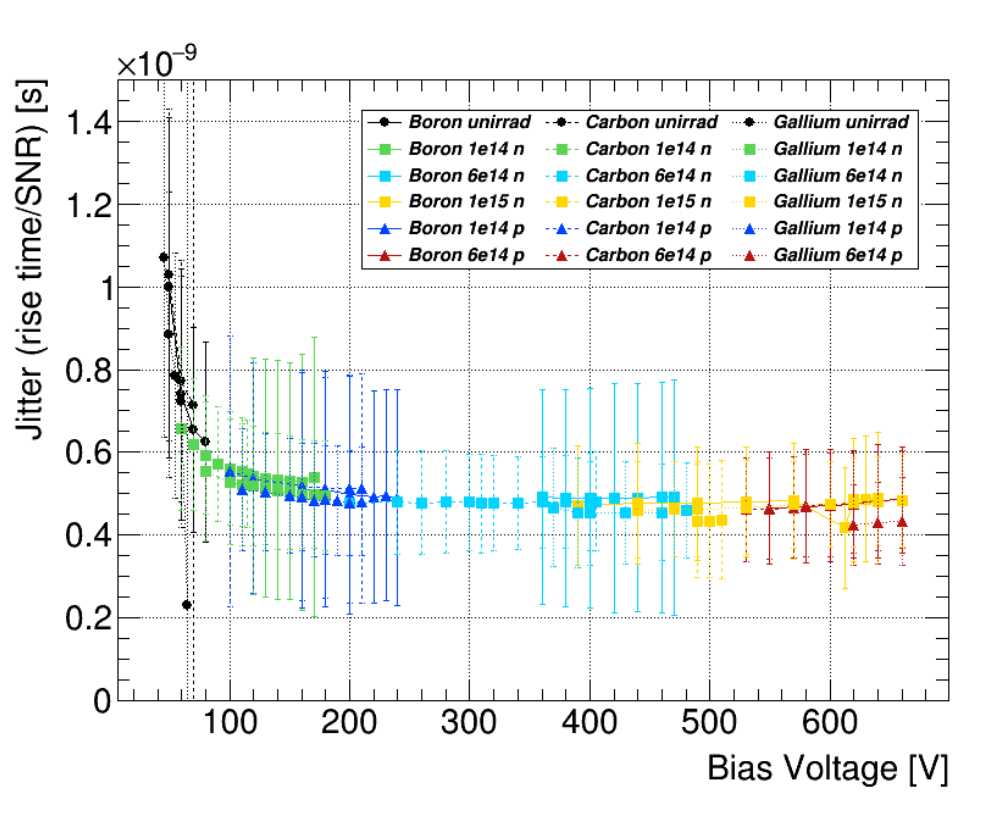
Data analysis tools



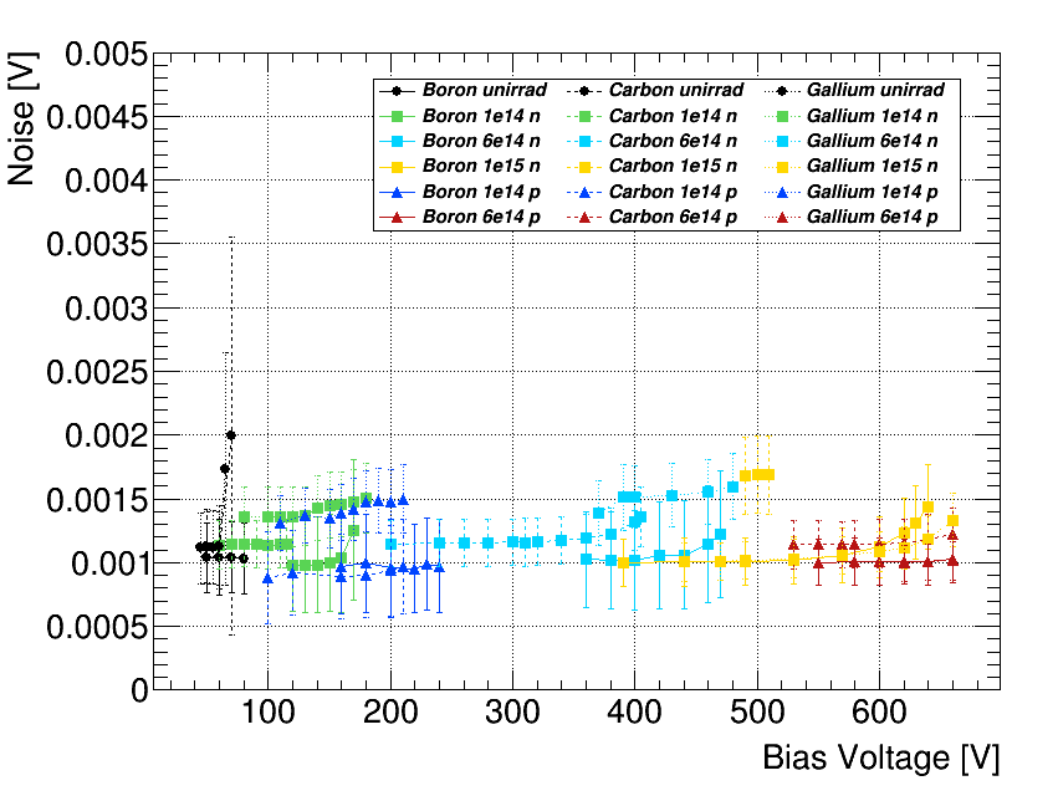
- Track reconstruction performed with **EUTelescope software v01-19-02 using GBL algorithm**
  - Requiring one hit in FE-I4 plane → resulting in ~30% of total events with an average FE-I4 efficiency of 99.6%
- Waveform processing performed with **LGADUtils framework v1.0 (C++ based)** developed at IFAE by V. Gkougkousis (https://indico.cern.ch/event/782573/#preview:2889703)
  - Match event information between telescope and oscilloscope discarding events without FE-I4 hits

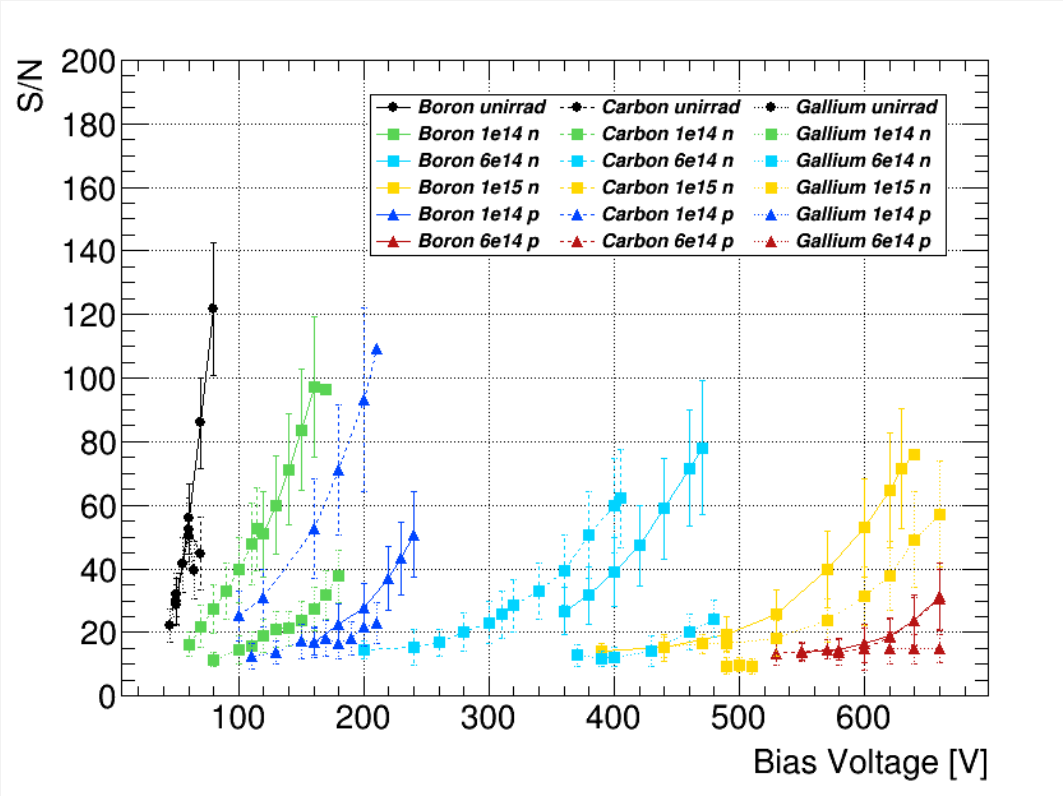
LGAD pulse properties





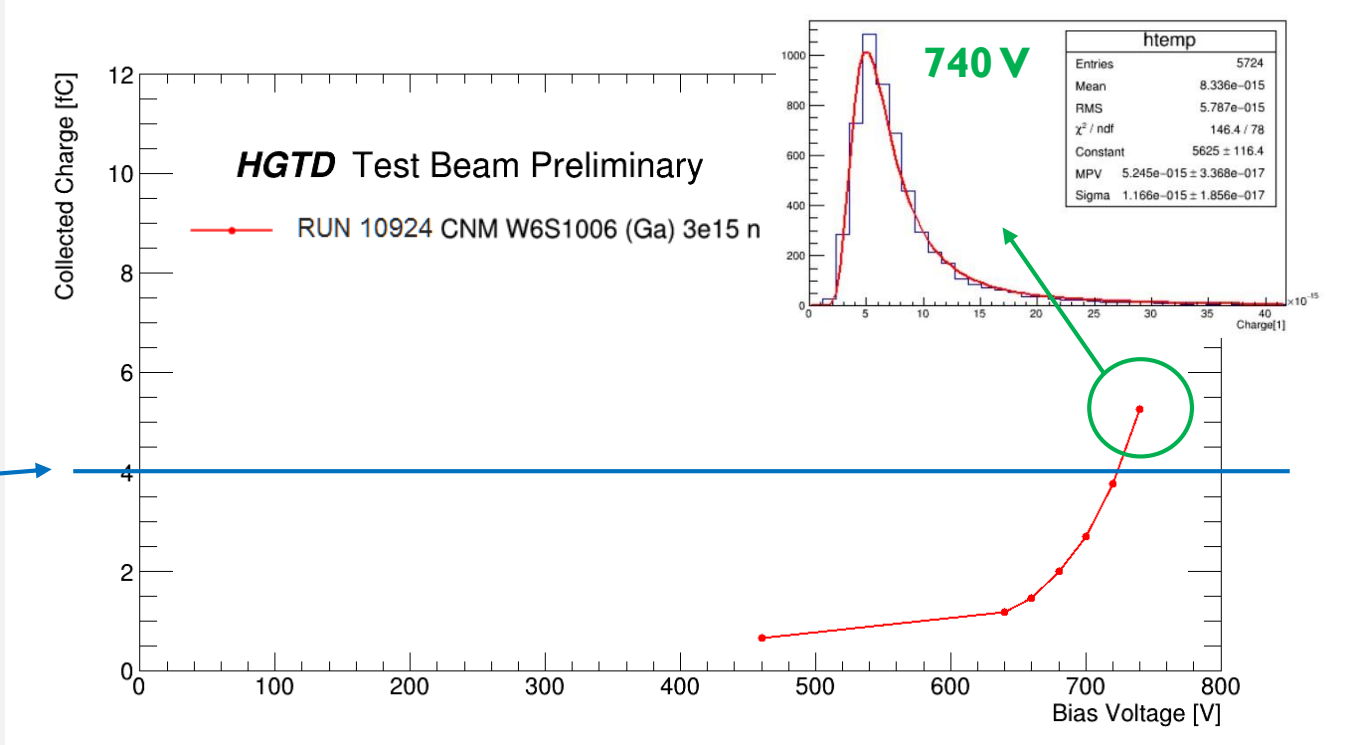
LGAD pulse properties





LGAD collected charge

- Charge calculated as the integral of the signal area for each recorded waveform after pedestal substraction
- At each voltage point the collected charge is given by the MPV value of the Landau-Gauss fit of the events charge distribution
- Performance of a CNM Gallium doped W6S1006 irradiated to 3×10^{15} n_{eq}/cm^2
- Collected charge as a function of bias voltage
  - Bias voltage range from 460 to 740 V
  - 2 fC at 680 V
  - Reaches 4 fC for optimal ALTIROC performance at bias voltage >720 V
  - At **740 V** collected charge is **5.3 fC**

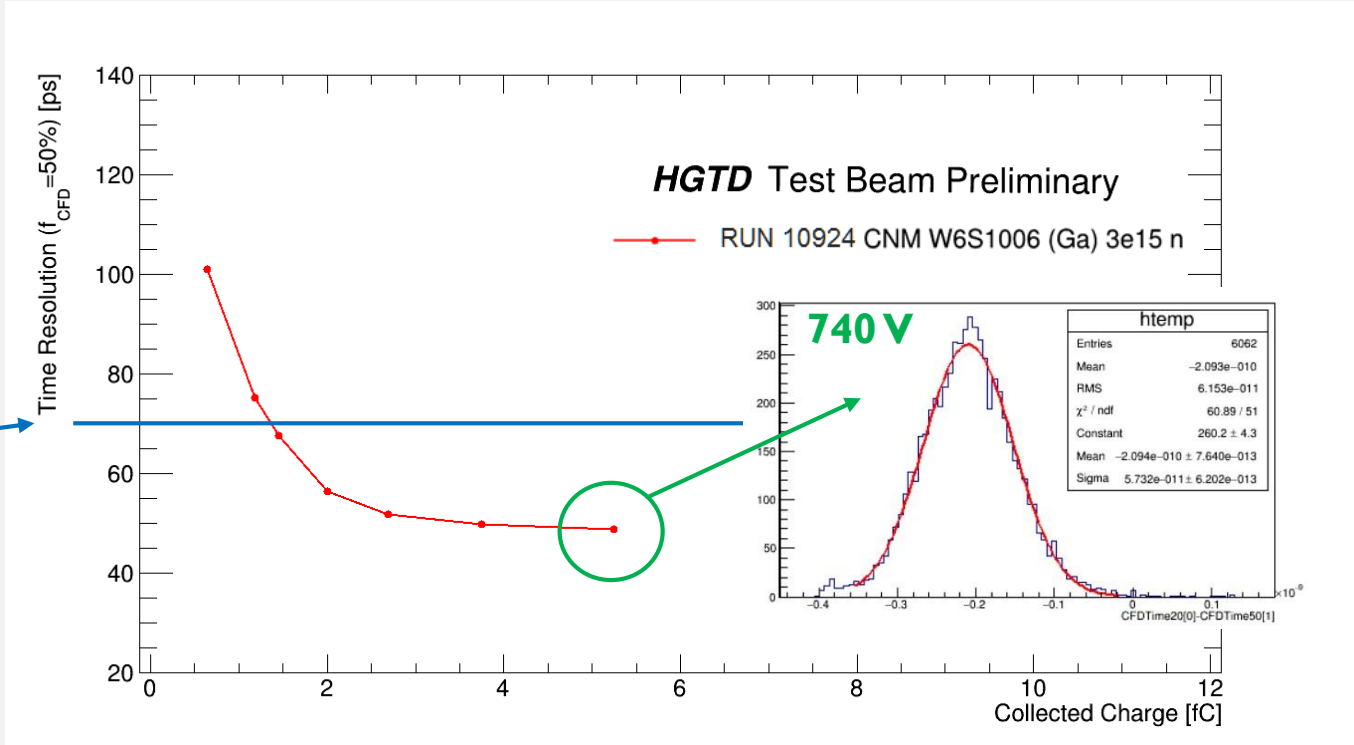


LGAD time resolution

- Timing distribution calculated as the difference between the time at f_{CFD}=50% for DUT and the time at f_{CFD}=20% for the unirradiated reference sensor

$$\Delta t = t_{DUT(f_{CFD}=50\%)} - t_{LGA35(f_{CFD}=20\%)}$$

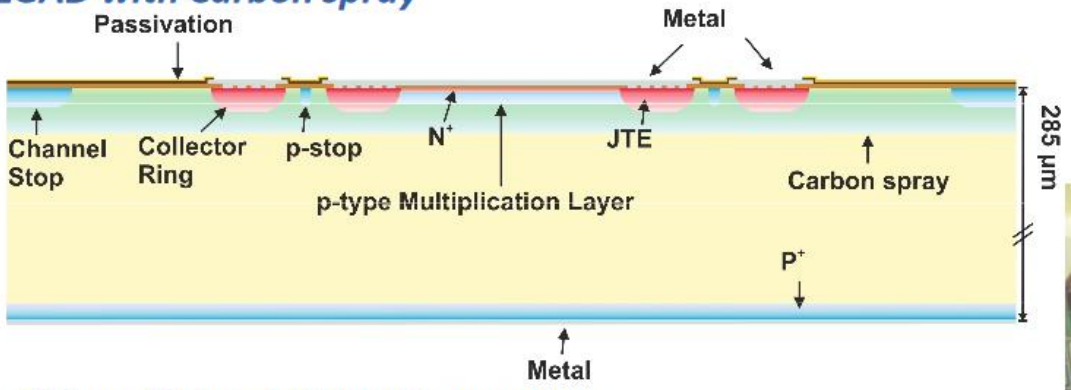
  - Fraction defined by the dominant contribution
    - unirradiated sensor → Landau fluctuations
    - Irradiated sensor → jitter (higher threshold)
- The time difference distribution is fitted with a Gaussian with the time resolution of the system defined as the σ of the Gaussian
- At **740 V**
  - **Time resolution** is **48 ps** (<70 ps requirement)
  - The contribution of the reference sensor is subtracted (29.7 ps at -28 °C)

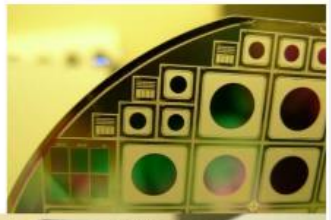


LGADs with C-spray

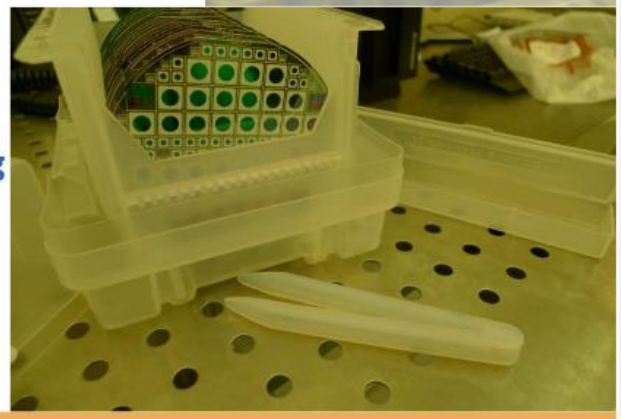
First measurements on LGAD with Carbon spray (run 9889)

LGAD with Carbon spray





- 300 µm high resistivity p-type wafers
- 5 PWell Implantation Dose
  - ✓ Co-diffusion of Boron, Phosphorous and Carbon will introduce some difference in the final doping profile. Carbon can reduce the Boron and Phosphorus diffusion. Because that variation, 5 Pwell imp. Doses have been implanted.



B-Ga doping profile

CV Profiling

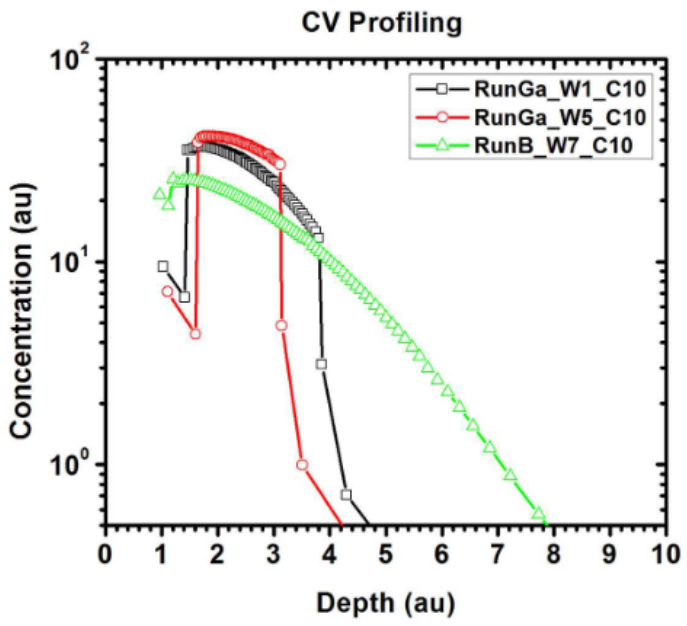


Figure shows the differences between Boron and Ga profiles.

Boron peak much **lower** than Gallium.

Boron diffusion seems **deeper** than Gallium diffusion.

Diffusion model of Ga still to be optimized. Necessary for the simulation.

Waiting for results from **SIMS**

Radiation hard studies results in Gregor´s talk at this workshop

AIDA2020 IP gap